



**CY7C1471V25**  
**CY7C1473V25**  
**CY7C1475V25**

## 72-Mbit (2M x 36/4M x 18/1M x 72) Flow-Through SRAM with NoBL™ Architecture

### Features

- No Bus Latency™ (NoBL™) architecture eliminates dead cycles between write and read cycles
- Supports up to 133 MHz bus operations with zero wait states
- Data is transferred on every clock
- Pin compatible and functionally equivalent to ZBT™ devices
- Internally self timed output buffer control to eliminate the need to use OE
- Registered inputs for flow through operation
- Byte Write capability
- 2.5V/1.8V IO supply (V<sub>DDQ</sub>)
- Fast clock-to-output times  
 — 6.5 ns (for 133-MHz device)
- Clock Enable ( $\overline{CEN}$ ) pin to enable clock and suspend operation
- Synchronous self timed writes
- Asynchronous Output Enable ( $\overline{OE}$ )
- CY7C1471V25, CY7C1473V25 available in JEDEC-standard Pb-free 100-pin TQFP, Pb-free and non-Pb-free 165-Ball FBGA package. CY7C1475V25 available in Pb-free and non-Pb-free 209-Ball FBGA package.
- Three Chip Enables ( $\overline{CE}_1$ ,  $CE_2$ ,  $\overline{CE}_3$ ) for simple depth expansion.
- Automatic power down feature available using ZZ mode or CE deselect.
- IEEE 1149.1 JTAG Boundary Scan compatible
- Burst Capability - linear or interleaved burst order
- Low standby power

### Functional Description<sup>[1]</sup>

The CY7C1471V25, CY7C1473V25, and CY7C1475V25 are 2.5V, 2M x 36/4M x 18/1M x 72 synchronous flow through burst SRAMs designed specifically to support unlimited true back-to-back read or write operations without the insertion of wait states. The CY7C1471V25, CY7C1473V25, and CY7C1475V25 are equipped with the advanced No Bus Latency (NoBL) logic required to enable consecutive read or write operations with data transferred on every clock cycle. This feature dramatically improves the throughput of data through the SRAM, especially in systems that require frequent write-read transitions.

All synchronous inputs pass through input registers controlled by the rising edge of the clock. The clock input is qualified by the Clock Enable ( $\overline{CEN}$ ) signal, which when deasserted suspends operation and extends the previous clock cycle. Maximum access delay from the clock rise is 6.5 ns (133-MHz device).

Write operations are controlled by two or four Byte Write Select ( $BW_x$ ) and a Write Enable ( $\overline{WE}$ ) input. All writes are conducted with on-chip synchronous self timed write circuitry.

Three synchronous Chip Enables ( $\overline{CE}_1$ ,  $CE_2$ ,  $\overline{CE}_3$ ) and an asynchronous Output Enable ( $\overline{OE}$ ) provide easy bank selection and output tri-state control. To avoid bus contention, the output drivers are synchronously tri-stated during the data portion of a write sequence.

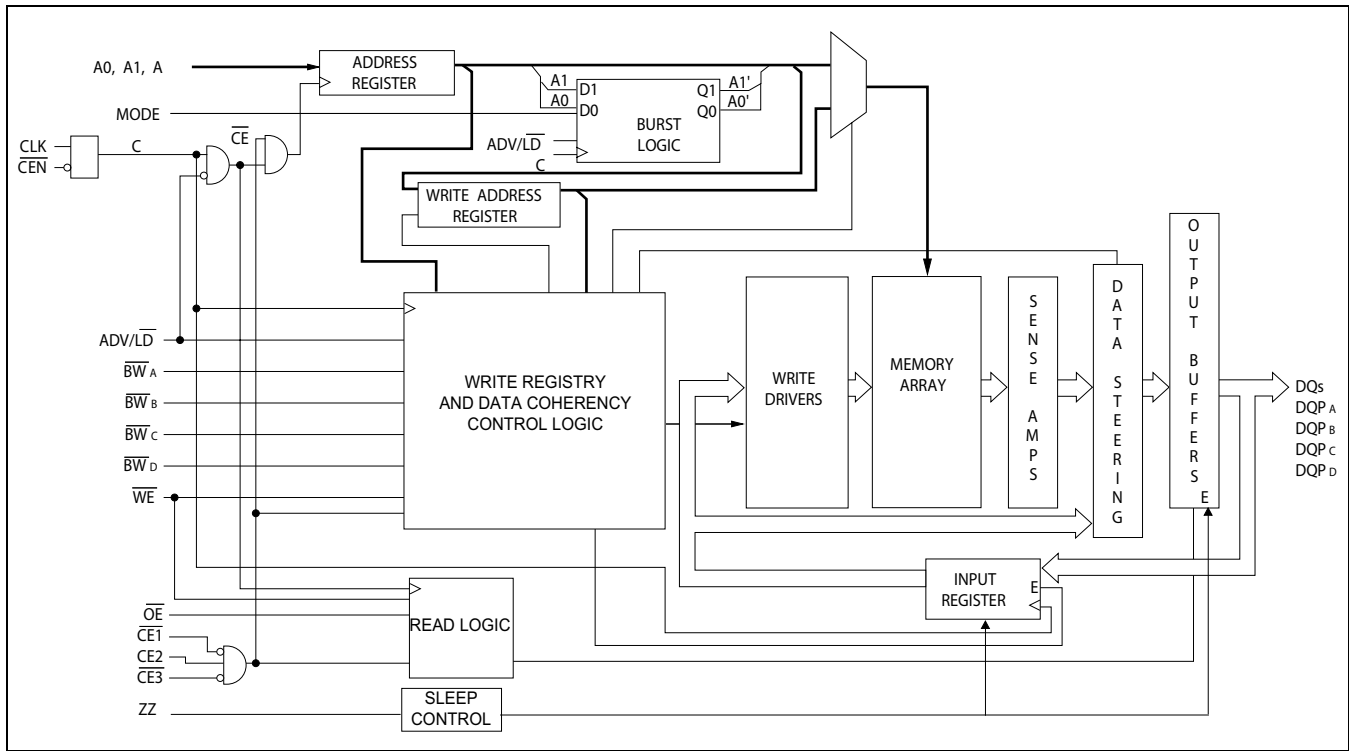
### Selection Guide

|                              | 133 MHz | 100 MHz | Unit |
|------------------------------|---------|---------|------|
| Maximum Access Time          | 6.5     | 8.5     | ns   |
| Maximum Operating Current    | 305     | 275     | mA   |
| Maximum CMOS Standby Current | 120     | 120     | mA   |

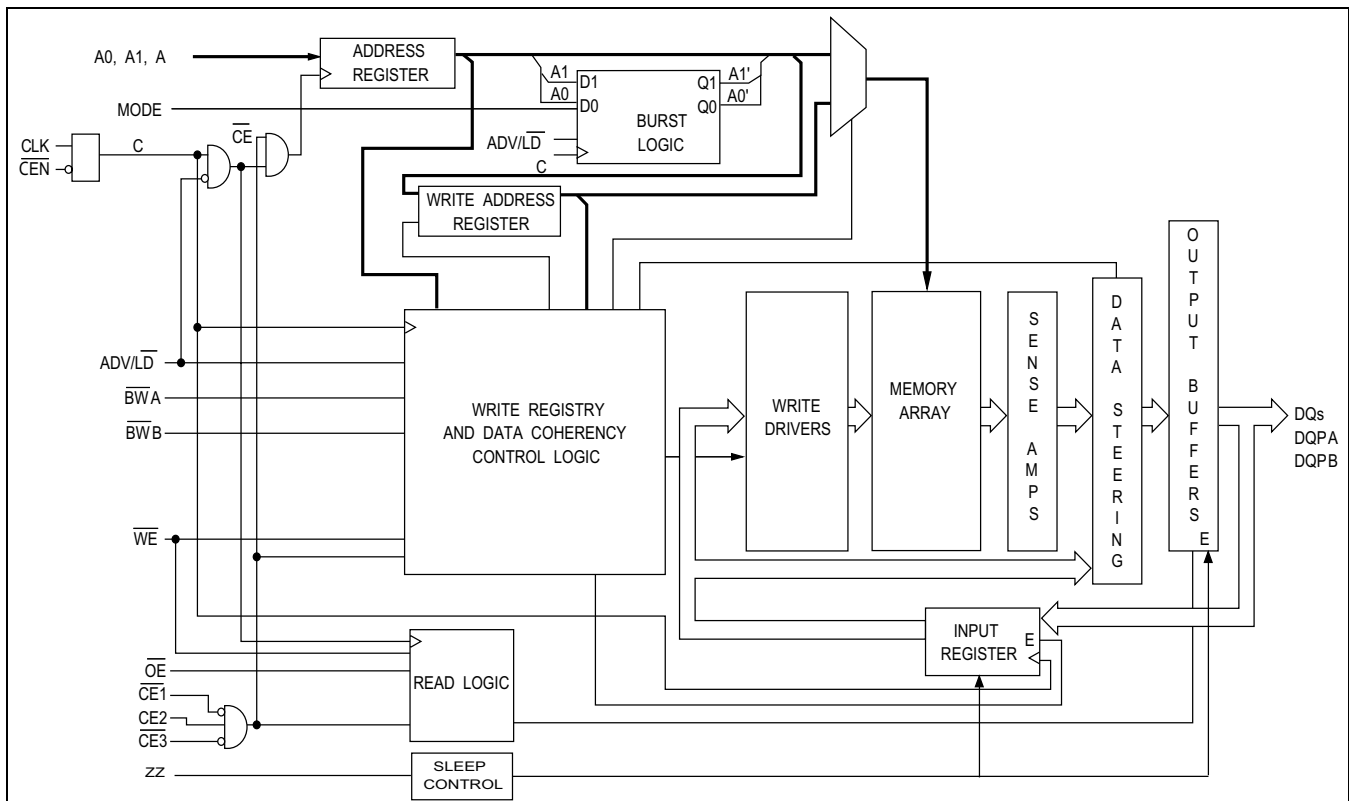
#### Note

1. For best practice recommendations, refer to the Cypress application note [AN1064, SRAM System Guidelines](#).

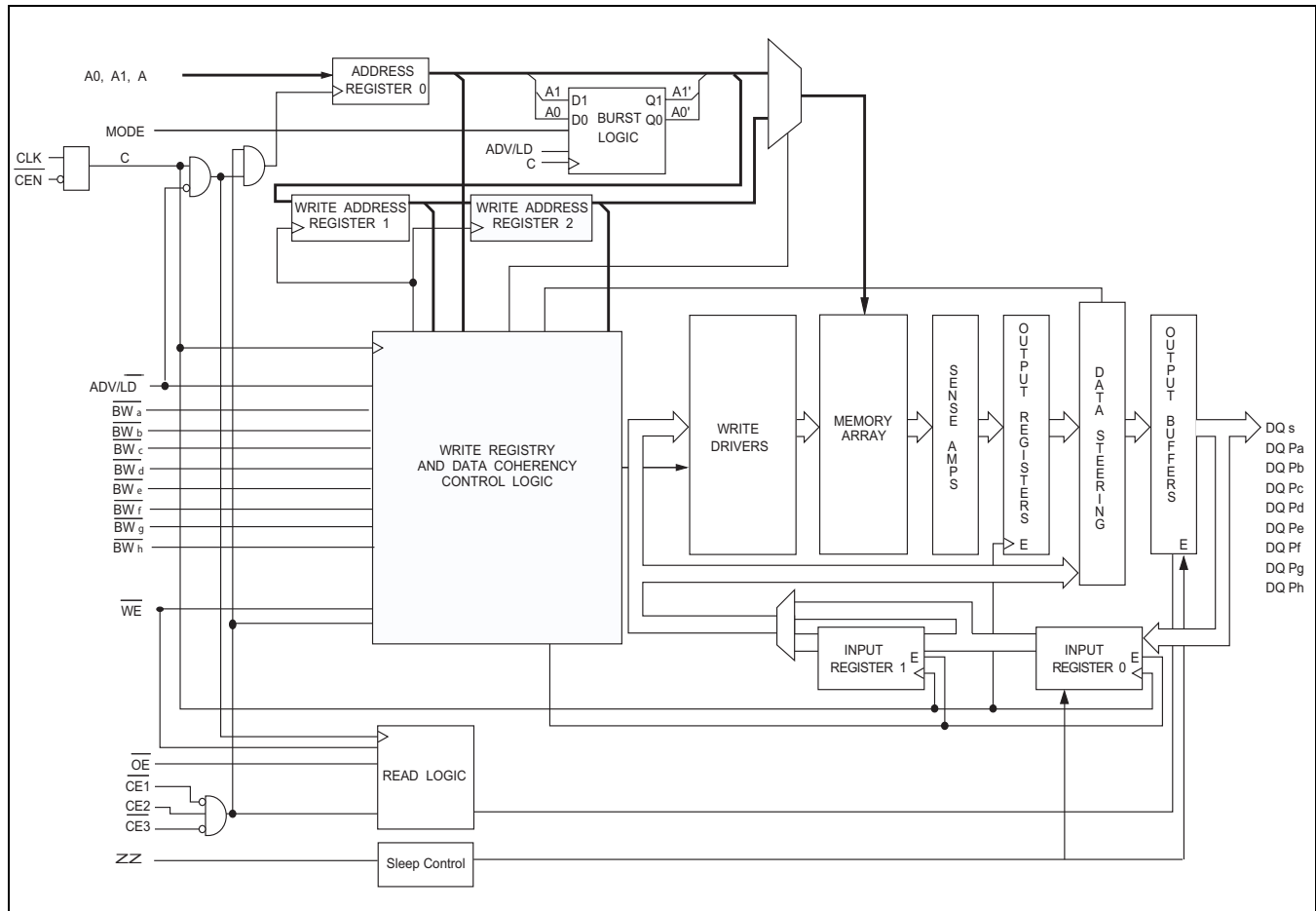
**Logic Block Diagram – CY7C1471V25 (2M x 36)**



**Logic Block Diagram – CY7C1473V25 (4M x 18)**

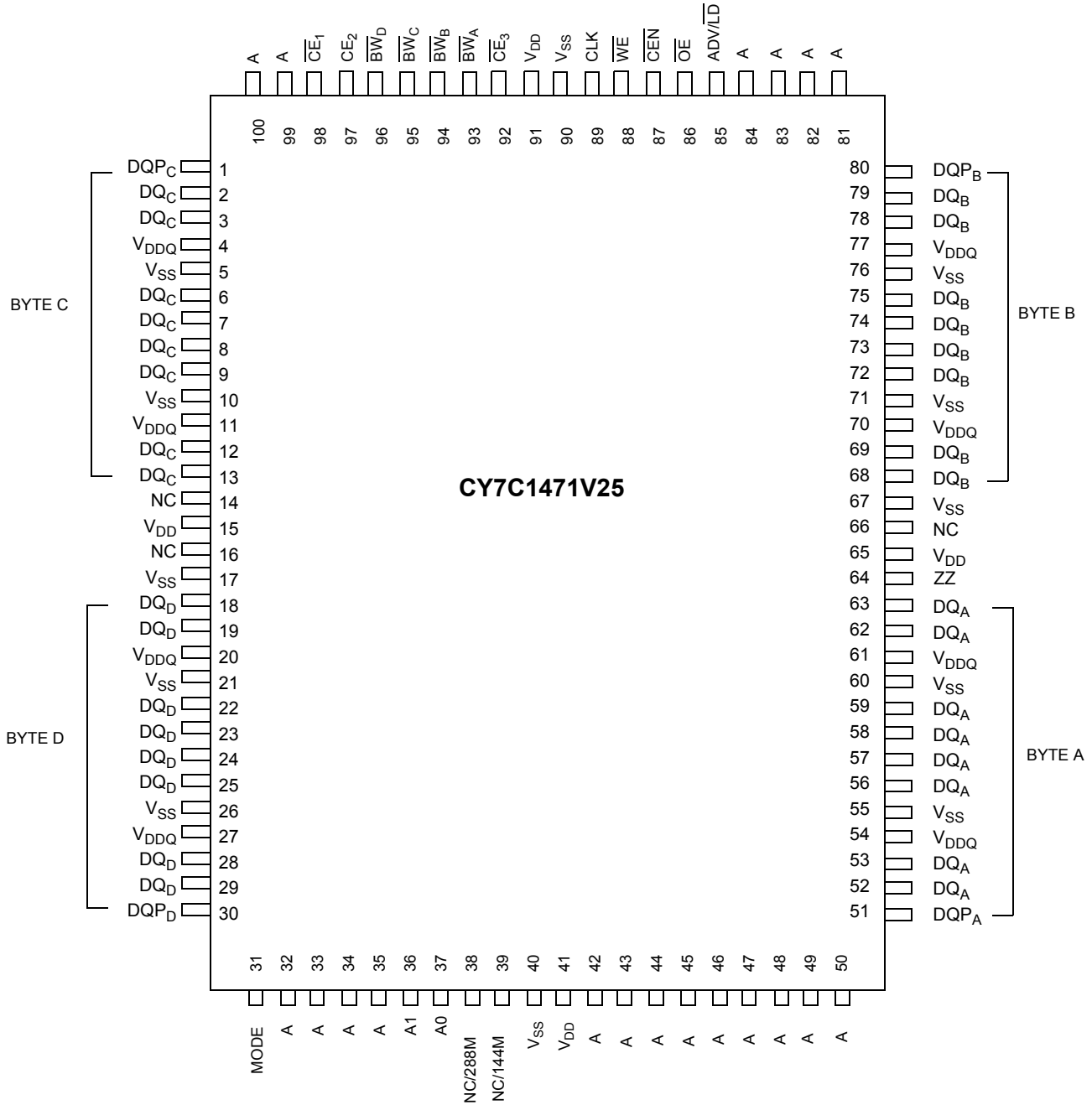


**Logic Block Diagram – CY7C1475V25 (1M x 72)**



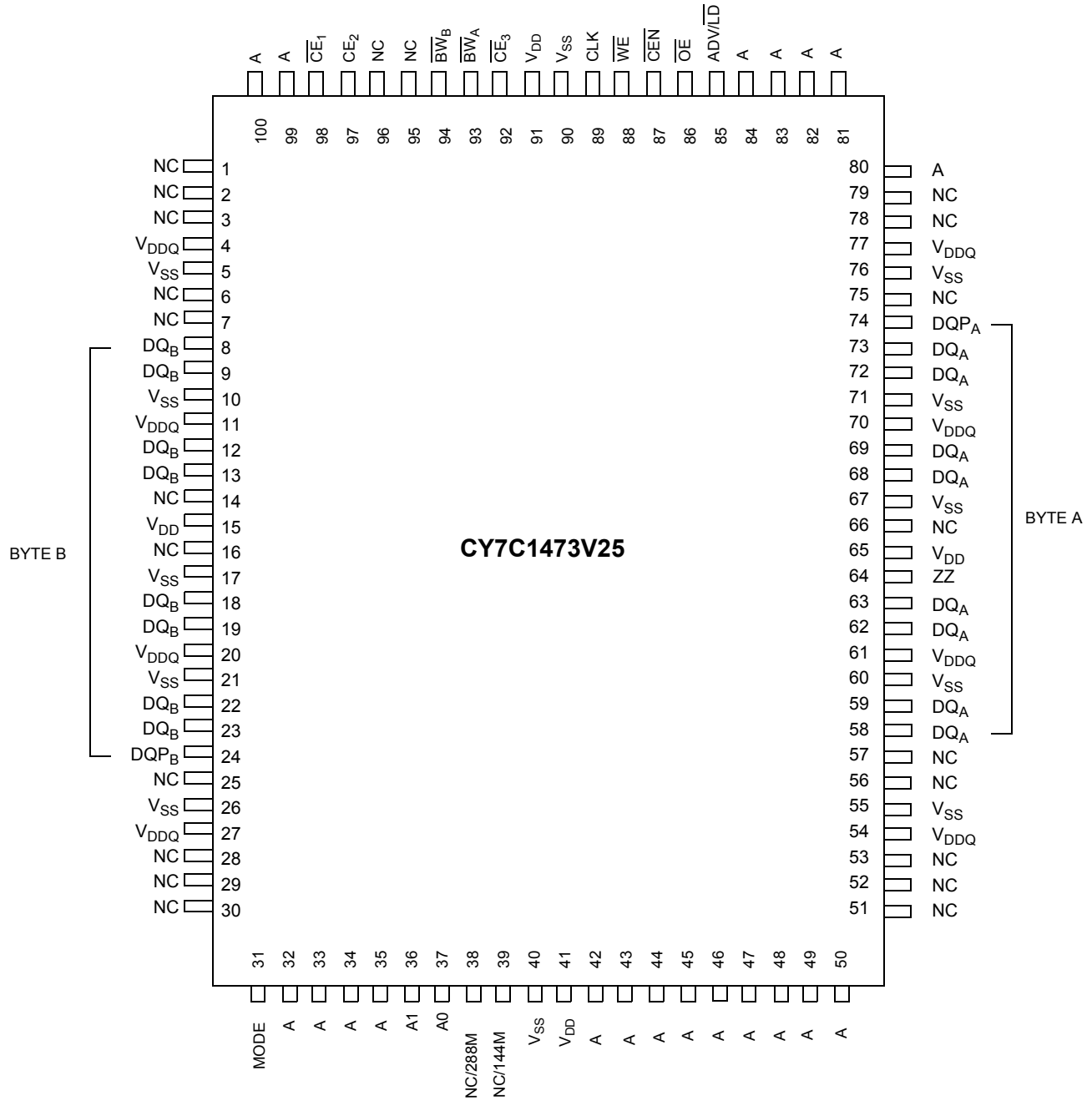
**Pin Configurations**

**100-Pin TQFP Pinout**



**Pin Configurations** (continued)

**100-Pin TQFP Pinout**



**Pin Configurations** (continued)

**165-Ball FBGA (15 x 17 x 1.4 mm) Pinout**  
**CY7C1471V25 (2M x 36)**

|          | 1                | 2               | 3                 | 4                 | 5                 | 6                 | 7                | 8               | 9                | 10              | 11               |
|----------|------------------|-----------------|-------------------|-------------------|-------------------|-------------------|------------------|-----------------|------------------|-----------------|------------------|
| <b>A</b> | NC/576M          | A               | $\overline{CE}_1$ | $\overline{BW}_C$ | $\overline{BW}_B$ | $\overline{CE}_3$ | $\overline{CEN}$ | ADV/LD          | A                | A               | NC               |
| <b>B</b> | NC/1G            | A               | CE2               | $\overline{BW}_D$ | $\overline{BW}_A$ | CLK               | $\overline{WE}$  | $\overline{OE}$ | A                | A               | NC               |
| <b>C</b> | DQP <sub>C</sub> | NC              | V <sub>DDQ</sub>  | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>SS</sub> | V <sub>DDQ</sub> | NC              | DQP <sub>B</sub> |
| <b>D</b> | DQ <sub>C</sub>  | DQ <sub>C</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>B</sub> | DQ <sub>B</sub>  |
| <b>E</b> | DQ <sub>C</sub>  | DQ <sub>C</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>B</sub> | DQ <sub>B</sub>  |
| <b>F</b> | DQ <sub>C</sub>  | DQ <sub>C</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>B</sub> | DQ <sub>B</sub>  |
| <b>G</b> | DQ <sub>C</sub>  | DQ <sub>C</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>B</sub> | DQ <sub>B</sub>  |
| <b>H</b> | NC               | NC              | NC                | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | NC               | NC              | ZZ               |
| <b>J</b> | DQ <sub>D</sub>  | DQ <sub>D</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>A</sub> | DQ <sub>A</sub>  |
| <b>K</b> | DQ <sub>D</sub>  | DQ <sub>D</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>A</sub> | DQ <sub>A</sub>  |
| <b>L</b> | DQ <sub>D</sub>  | DQ <sub>D</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>A</sub> | DQ <sub>A</sub>  |
| <b>M</b> | DQ <sub>D</sub>  | DQ <sub>D</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>A</sub> | DQ <sub>A</sub>  |
| <b>N</b> | DQP <sub>D</sub> | NC              | V <sub>DDQ</sub>  | V <sub>SS</sub>   | NC                | NC                | NC               | V <sub>SS</sub> | V <sub>DDQ</sub> | NC              | DQP <sub>A</sub> |
| <b>P</b> | NC/144M          | A               | A                 | A                 | TDI               | A1                | TDO              | A               | A                | A               | NC/288M          |
| <b>R</b> | MODE             | A               | A                 | A                 | TMS               | A0                | TCK              | A               | A                | A               | A                |

**CY7C1473V25 (4M x 18)**

|          | 1                | 2               | 3                 | 4                 | 5                 | 6                 | 7                | 8               | 9                | 10              | 11               |
|----------|------------------|-----------------|-------------------|-------------------|-------------------|-------------------|------------------|-----------------|------------------|-----------------|------------------|
| <b>A</b> | NC/576M          | A               | $\overline{CE}_1$ | $\overline{BW}_B$ | NC                | $\overline{CE}_3$ | $\overline{CEN}$ | ADV/LD          | A                | A               | A                |
| <b>B</b> | NC/1G            | A               | CE2               | NC                | $\overline{BW}_A$ | CLK               | $\overline{WE}$  | $\overline{OE}$ | A                | A               | NC               |
| <b>C</b> | NC               | NC              | V <sub>DDQ</sub>  | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>SS</sub> | V <sub>DDQ</sub> | NC              | DQP <sub>A</sub> |
| <b>D</b> | NC               | DQ <sub>B</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | NC              | DQ <sub>A</sub>  |
| <b>E</b> | NC               | DQ <sub>B</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | NC              | DQ <sub>A</sub>  |
| <b>F</b> | NC               | DQ <sub>B</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | NC              | DQ <sub>A</sub>  |
| <b>G</b> | NC               | DQ <sub>B</sub> | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | NC              | DQ <sub>A</sub>  |
| <b>H</b> | NC               | NC              | NC                | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | NC               | NC              | ZZ               |
| <b>J</b> | DQ <sub>B</sub>  | NC              | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>A</sub> | NC               |
| <b>K</b> | DQ <sub>B</sub>  | NC              | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>A</sub> | NC               |
| <b>L</b> | DQ <sub>B</sub>  | NC              | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>A</sub> | NC               |
| <b>M</b> | DQ <sub>B</sub>  | NC              | V <sub>DDQ</sub>  | V <sub>DD</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>   | V <sub>SS</sub>  | V <sub>DD</sub> | V <sub>DDQ</sub> | DQ <sub>A</sub> | NC               |
| <b>N</b> | DQP <sub>B</sub> | NC              | V <sub>DDQ</sub>  | V <sub>SS</sub>   | NC                | NC                | NC               | V <sub>SS</sub> | V <sub>DDQ</sub> | NC              | NC               |
| <b>P</b> | NC/144M          | A               | A                 | A                 | TDI               | A1                | TDO              | A               | A                | A               | NC/288M          |
| <b>R</b> | MODE             | A               | A                 | A                 | TMS               | A0                | TCK              | A               | A                | A               | A                |

**Pin Configurations** (continued)

**209-Ball FBGA (14 x 22 x 1.76 mm) Pinout**  
**CY7C1475V25 (1M × 72)**

|          | 1    | 2    | 3                | 4                | 5               | 6               | 7               | 8                | 9                | 10   | 11   |
|----------|------|------|------------------|------------------|-----------------|-----------------|-----------------|------------------|------------------|------|------|
| <b>A</b> | DQg  | DQg  | A                | CE <sub>2</sub>  | A               | ADV/LD          | A               | CE <sub>3</sub>  | A                | DQb  | DQb  |
| <b>B</b> | DQg  | DQg  | BWS <sub>c</sub> | BWS <sub>g</sub> | NC              | WE              | A               | BWS <sub>b</sub> | BWS <sub>f</sub> | DQb  | DQb  |
| <b>C</b> | DQg  | DQg  | BWS <sub>h</sub> | BWS <sub>d</sub> | NC/576M         | CE <sub>1</sub> | NC              | BWS <sub>e</sub> | BWS <sub>a</sub> | DQb  | DQb  |
| <b>D</b> | DQg  | DQg  | V <sub>SS</sub>  | NC               | NC/1G           | OE              | NC              | NC               | V <sub>SS</sub>  | DQb  | DQb  |
| <b>E</b> | DQPg | DQPc | V <sub>DDQ</sub> | V <sub>DDQ</sub> | V <sub>DD</sub> | V <sub>DD</sub> | V <sub>DD</sub> | V <sub>DDQ</sub> | V <sub>DDQ</sub> | DQPf | DQPb |
| <b>F</b> | DQc  | DQc  | V <sub>SS</sub>  | V <sub>SS</sub>  | V <sub>SS</sub> | NC              | V <sub>SS</sub> | V <sub>SS</sub>  | V <sub>SS</sub>  | DQf  | DQf  |
| <b>G</b> | DQc  | DQc  | V <sub>DDQ</sub> | V <sub>DDQ</sub> | V <sub>DD</sub> | NC              | V <sub>DD</sub> | V <sub>DDQ</sub> | V <sub>DDQ</sub> | DQf  | DQf  |
| <b>H</b> | DQc  | DQc  | V <sub>SS</sub>  | V <sub>SS</sub>  | V <sub>SS</sub> | NC              | V <sub>SS</sub> | V <sub>SS</sub>  | V <sub>SS</sub>  | DQf  | DQf  |
| <b>J</b> | DQc  | DQc  | V <sub>DDQ</sub> | V <sub>DDQ</sub> | V <sub>DD</sub> | NC              | V <sub>DD</sub> | V <sub>DDQ</sub> | V <sub>DDQ</sub> | DQf  | DQf  |
| <b>K</b> | NC   | NC   | CLK              | NC               | V <sub>SS</sub> | CEN             | V <sub>SS</sub> | NC               | NC               | NC   | NC   |
| <b>L</b> | DQh  | DQh  | V <sub>DDQ</sub> | V <sub>DDQ</sub> | V <sub>DD</sub> | NC              | V <sub>DD</sub> | V <sub>DDQ</sub> | V <sub>DDQ</sub> | DQa  | DQa  |
| <b>M</b> | DQh  | DQh  | V <sub>SS</sub>  | V <sub>SS</sub>  | V <sub>SS</sub> | NC              | V <sub>SS</sub> | V <sub>SS</sub>  | V <sub>SS</sub>  | DQa  | DQa  |
| <b>N</b> | DQh  | DQh  | V <sub>DDQ</sub> | V <sub>DDQ</sub> | V <sub>DD</sub> | NC              | V <sub>DD</sub> | V <sub>DDQ</sub> | V <sub>DDQ</sub> | DQa  | DQa  |
| <b>P</b> | DQh  | DQh  | V <sub>SS</sub>  | V <sub>SS</sub>  | V <sub>SS</sub> | ZZ              | V <sub>SS</sub> | V <sub>SS</sub>  | V <sub>SS</sub>  | DQa  | DQa  |
| <b>R</b> | DQPd | DQPb | V <sub>DDQ</sub> | V <sub>DDQ</sub> | V <sub>DD</sub> | V <sub>DD</sub> | V <sub>DD</sub> | V <sub>DDQ</sub> | V <sub>DDQ</sub> | DQPc | DQPd |
| <b>T</b> | DQd  | DQd  | V <sub>SS</sub>  | NC               | NC              | MODE            | NC              | NC               | V <sub>SS</sub>  | DQe  | DQe  |
| <b>U</b> | DQd  | DQd  | NC/144M          | A                | A               | A               | A               | A                | NC/288M          | DQe  | DQe  |
| <b>V</b> | DQd  | DQd  | A                | A                | A               | A1              | A               | A                | A                | DQe  | DQe  |
| <b>W</b> | DQd  | DQd  | TMS              | TDI              | A               | A0              | A               | TDO              | TCK              | DQe  | DQe  |

## Pin Definitions

| Name   | IO                             | Description   |
|--|--------------------------------|---|
| A <sub>0</sub> , A <sub>1</sub> , A  | Input-Synchronous              | <b>Address Inputs used to select one of the address locations.</b> Sampled at the rising edge of the CLK. A <sub>[1:0]</sub> are fed to the two-bit burst counter.  |
| $\overline{BW}_A$ , $\overline{BW}_B$ ,<br>$\overline{BW}_C$ , $\overline{BW}_D$ ,<br>$\overline{BW}_E$ , $\overline{BW}_F$ ,<br>$\overline{BW}_G$ , $\overline{BW}_H$ | Input-Synchronous              | <b>Byte Write Inputs, Active LOW.</b> Qualified with $\overline{WE}$ to conduct writes to the SRAM. Sampled on the rising edge of CLK.  |
| $\overline{WE}$  | Input-Synchronous              | <b>Write Enable Input, Active LOW.</b> Sampled on the rising edge of CLK if $\overline{CEN}$ is active LOW. This signal must be asserted LOW to initiate a write sequence.  |
| ADV/LD   | Input-Synchronous              | <b>Advance/Load Input.</b> Used to advance the on-chip address counter or load a new address. When HIGH (and $\overline{CEN}$ is asserted LOW) the internal burst counter is advanced. When LOW, a new address can be loaded into the device for an access. After being deselected, ADV/LD must be driven LOW to load a new address.  |
| CLK  | Input-Clock                    | <b>Clock Input.</b> Captures all synchronous inputs to the device. CLK is qualified with $\overline{CEN}$ . CLK is only recognized if $\overline{CEN}$ is active LOW.   |
| $\overline{CE}_1$  | Input-Synchronous              | <b>Chip Enable 1 Input, Active LOW.</b> Sampled on the rising edge of CLK. Used in conjunction with $\overline{CE}_2$ and $\overline{CE}_3$ to select or deselect the device.   |
| $\overline{CE}_2$  | Input-Synchronous              | <b>Chip Enable 2 Input, Active HIGH.</b> Sampled on the rising edge of CLK. Used in conjunction with $\overline{CE}_1$ and $\overline{CE}_3$ to select or deselect the device.  |
| $\overline{CE}_3$  | Input-Synchronous              | <b>Chip Enable 3 Input, Active LOW.</b> Sampled on the rising edge of CLK. Used in conjunction with $\overline{CE}_1$ and $\overline{CE}_2$ to select or deselect the device.   |
| $\overline{OE}$  | Input-Asynchronous             | <b>Output Enable, Asynchronous Input, Active LOW.</b> Combined with the synchronous logic block inside the device to control the direction of the IO pins. When LOW, the IO pins are enabled to behave as outputs. When deasserted HIGH, IO pins are tri-stated, and act as input data pins. $\overline{OE}$ is masked during the data portion of a write sequence, during the first clock when emerging from a deselected state, when the device has been deselected.  |
| $\overline{CEN}$   | Input-Synchronous              | <b>Clock Enable Input, Active LOW.</b> When asserted LOW the clock signal is recognized by the SRAM. When deasserted HIGH the clock signal is masked. Because deasserting $\overline{CEN}$ does not deselect the device, $\overline{CEN}$ can be used to extend the previous cycle when required.   |
| ZZ   | Input-Asynchronous             | <b>ZZ “Sleep” Input.</b> This active HIGH input places the device in a non-time-critical “sleep” condition with data integrity preserved. For normal operation, this pin has to be LOW or left floating. ZZ pin has an internal pull down.  |
| DQ <sub>s</sub>  | IO-Synchronous                 | <b>Bidirectional Data IO Lines.</b> As inputs, they feed into an on-chip data register that is triggered by the rising edge of CLK. As outputs, they deliver the data contained in the memory location specified by the addresses presented during the previous clock rise of the read cycle. The direction of the pins is controlled by $\overline{OE}$ . When $\overline{OE}$ is asserted LOW, the pins behave as outputs. When HIGH, DQ <sub>s</sub> and DQP <sub>x</sub> are placed in a tri-state condition. The outputs are automatically tri-stated during the data portion of a write sequence, during the first clock when emerging from a deselected state, and when the device is deselected, regardless of the state of $\overline{OE}$ . |
| DQP <sub>x</sub>   | IO-Synchronous                 | <b>Bidirectional Data Parity IO Lines.</b> Functionally, these signals are identical to DQ <sub>s</sub> . During write sequences, DQP <sub>x</sub> is controlled by $\overline{BW}_x$ correspondingly.  |
| MODE   | Input Strap Pin                | <b>Mode Input. Selects the burst order of the device.</b> When tied to Gnd selects linear burst sequence. When tied to V <sub>DD</sub> or left floating selects interleaved burst sequence.   |
| V <sub>DD</sub>  | Power Supply                   | <b>Power supply inputs to the core of the device.</b>   |
| V <sub>DDQ</sub>   | IO Power Supply                | <b>Power supply for the IO circuitry.</b>   |
| V <sub>SS</sub>  | Ground                         | <b>Ground for the device.</b>   |
| TDO  | JTAG serial output Synchronous | <b>Serial data-out to the JTAG circuit.</b> Delivers data on the negative edge of TCK. If the JTAG feature is not used, this pin must be left unconnected. This pin is not available on TQFP packages.  |



## Pin Definitions (continued)

| Name | IO                               | Description   |
|------|----------------------------------|---|
| TDI  | JTAG serial input<br>Synchronous | <b>Serial data-In to the JTAG circuit.</b> Sampled on the rising edge of TCK. If the JTAG feature is not used, this pin can be left floating or connected to $V_{DD}$ through a pull up resistor. This pin is not available on TQFP packages. |
| TMS  | JTAG serial input<br>Synchronous | <b>Serial data-In to the JTAG circuit.</b> Sampled on the rising edge of TCK. If the JTAG feature is not used, this pin can be disconnected or connected to $V_{DD}$ . This pin is not available on TQFP packages.                            |
| TCK  | JTAG-Clock                       | <b>Clock input to the JTAG circuitry.</b> If the JTAG feature is not used, this pin must be connected to $V_{SS}$ . This pin is not available on TQFP packages.   |
| NC   | -                                | <b>No Connects.</b> Not internally connected to the die. 144M, 288M, 576M, and 1G are address expansion pins and are not internally connected to the die.   |

## Functional Overview

The CY7C1471V25, CY7C1473V25, and CY7C1475V25 are synchronous flow through burst SRAMs designed specifically to eliminate wait states during write-read transitions. All synchronous inputs pass through input registers controlled by the rising edge of the clock. The clock signal is qualified with the Clock Enable input signal ( $\overline{CEN}$ ). If  $\overline{CEN}$  is HIGH, the clock signal is not recognized and all internal states are maintained. All synchronous operations are qualified with  $\overline{CEN}$ . Maximum access delay from the clock rise ( $t_{CDV}$ ) is 6.5 ns (133-MHz device).

Accesses are initiated by asserting all three Chip Enables ( $\overline{CE}_1$ ,  $\overline{CE}_2$ ,  $\overline{CE}_3$ ) active at the rising edge of the clock. If  $\overline{CEN}$  is active LOW and  $\overline{ADV/LD}$  is asserted LOW, the address presented to the device is latched. The access can either be a read or write operation, depending on the status of the Write Enable ( $\overline{WE}$ ). Byte Write Select ( $\overline{BW}_X$ ) can be used to conduct Byte Write operations.

Write operations are qualified by the  $\overline{WE}$ . All writes are simplified with on-chip synchronous self timed write circuitry.

Three synchronous Chip Enables ( $\overline{CE}_1$ ,  $\overline{CE}_2$ ,  $\overline{CE}_3$ ) and an asynchronous Output Enable ( $\overline{OE}$ ) simplify depth expansion. All operations (reads, writes, and deselections) are pipelined.  $\overline{ADV/LD}$  must be driven LOW after the device is deselected to load a new address for the next operation.

### Single Read Accesses

A read access is initiated when the following conditions are satisfied at clock rise: (1)  $\overline{CEN}$  is asserted LOW, (2)  $\overline{CE}_1$ ,  $\overline{CE}_2$ , and  $\overline{CE}_3$  are ALL asserted active, (3)  $\overline{WE}$  is deasserted HIGH, and (4)  $\overline{ADV/LD}$  is asserted LOW. The address presented to the address inputs is latched into the Address Register and presented to the memory array and control logic. The control logic determines that a read access is in progress and allows the requested data to propagate to the output buffers. The data is available within 6.5 ns (133-MHz device) provided  $\overline{OE}$  is active LOW. After the first clock of the read access, the output buffers are controlled by  $\overline{OE}$  and the internal control logic.  $\overline{OE}$  must be driven LOW to drive out the requested data. On the subsequent clock, another operation (read/write/deselect) can be initiated. When the SRAM is deselected at clock rise by one of the chip enable signals, the output is tri-stated immediately.

### Burst Read Accesses

The CY7C1471V25, CY7C1473V25, and CY7C1475V25 has an on-chip burst counter that enables the user the ability to supply a single address and conduct up to four reads without reasserting the address inputs.  $\overline{ADV/LD}$  must be driven LOW to load a new address into the SRAM, as described in the Single Read Access section. The sequence of the burst counter is determined by the MODE input signal. A LOW input on MODE selects a linear burst mode, a HIGH selects an interleaved burst sequence. Both burst counters use A0 and A1 in the burst sequence, and wraps around when incremented sufficiently. A HIGH input on  $\overline{ADV/LD}$  increments the internal burst counter regardless of the state of chip enable inputs or  $\overline{WE}$ .  $\overline{WE}$  is latched at the beginning of a burst cycle. Therefore, the type of access (read or write) is maintained throughout the burst sequence.

### Single Write Accesses

Write accesses are initiated when these conditions are satisfied at clock rise:

- $\overline{CEN}$  is asserted LOW
- $\overline{CE}_1$ ,  $\overline{CE}_2$ , and  $\overline{CE}_3$  are ALL asserted active
- $\overline{WE}$  is asserted LOW.

The address presented to the address bus is loaded into the Address Register. The write signals are latched into the Control Logic block. The data lines are automatically tri-stated regardless of the state of the  $\overline{OE}$  input signal. This allows the external logic to present the data on DQs and DQP<sub>X</sub>.

On the next clock rise the data presented to DQs and DQP<sub>X</sub> (or a subset for Byte Write operations, see "Truth Table for Read/Write" on page 12 for details) inputs is latched into the device and the write is complete. Additional accesses (read/write/deselect) can be initiated on this cycle.

The data written during the write operation is controlled by  $\overline{BW}_X$  signals. The CY7C1471V25, CY7C1473V25, and CY7C1475V25 provide Byte Write capability that is described in the "Truth Table for Read/Write" on page 12. The input  $\overline{WE}$  with the selected  $\overline{BW}_X$  input selectively writes to only the desired bytes. Bytes not selected during a Byte Write operation remain unaltered. A synchronous self timed write mechanism is provided to simplify the write operations. Byte Write capability is included to greatly simplify read/modify/write sequences, which can be reduced to simple byte write operations.

Because the CY7C1471V25, CY7C1473V25, and CY7C1475V25 are common IO devices, data must not be driven into the device while the outputs are active. The OE can be deasserted HIGH before presenting data to the DQs and DQP<sub>X</sub> inputs. This tri-states the output drivers. As a safety precaution, DQs and DQP<sub>X</sub> are automatically tri-stated during the data portion of a write cycle, regardless of the state of OE.

**Burst Write Accesses**

The CY7C1471V25, CY7C1473V25, and CY7C1475V25 have an on-chip burst counter that enables the user to supply a single address and conduct up to four Write operations without reasserting the address inputs. ADV/LD must be driven LOW to load the initial address, as described in the Single Write Access section. When ADV/LD is driven HIGH on the subsequent clock rise, the Chip Enables (CE<sub>1</sub>, CE<sub>2</sub>, and CE<sub>3</sub>) and WE inputs are ignored and the burst counter is incremented. The correct BW<sub>X</sub> inputs must be driven in each cycle of the Burst Write, to write the correct bytes of data.

**Sleep Mode**

The ZZ input pin is an asynchronous input. Asserting ZZ places the SRAM in a power conservation “sleep” mode. Two clock cycles are required to enter into or exit from this “sleep” mode. While in this mode, data integrity is guaranteed. Accesses pending when entering the “sleep” mode are not considered valid nor is the completion of the operation guaranteed. The device must be deselected before entering the “sleep” mode. CE<sub>1</sub>, CE<sub>2</sub>, and CE<sub>3</sub>, must remain inactive for the duration of t<sub>ZZREC</sub> after the ZZ input returns LOW.

**ZZ Mode Electrical Characteristics**

| Parameter          | Description                       | Test Conditions             | Min               | Max               | Unit |
|--------------------|-----------------------------------|-----------------------------|-------------------|-------------------|------|
| I <sub>DDZZ</sub>  | Sleep mode standby current        | ZZ ≥ V <sub>DD</sub> – 0.2V |                   | 120               | mA   |
| t <sub>ZZS</sub>   | Device operation to ZZ            | ZZ ≥ V <sub>DD</sub> – 0.2V |                   | 2t <sub>CYC</sub> | ns   |
| t <sub>ZZREC</sub> | ZZ recovery time                  | ZZ ≤ 0.2V                   | 2t <sub>CYC</sub> |                   | ns   |
| t <sub>ZZI</sub>   | ZZ active to sleep current        | This parameter is sampled   |                   | 2t <sub>CYC</sub> | ns   |
| t <sub>RZZI</sub>  | ZZ Inactive to exit sleep current | This parameter is sampled   | 0                 |                   | ns   |

**Interleaved Burst Address Table  
(MODE = Floating or V<sub>DD</sub>)**

| First Address A1: A0 | Second Address A1: A0 | Third Address A1: A0 | Fourth Address A1: A0 |
|----------------------|-----------------------|----------------------|-----------------------|
| 00                   | 01                    | 10                   | 11                    |
| 01                   | 00                    | 11                   | 10                    |
| 10                   | 11                    | 00                   | 01                    |
| 11                   | 10                    | 01                   | 00                    |

**Linear Burst Address Table  
(MODE = GND)**

| First Address A1: A0 | Second Address A1: A0 | Third Address A1: A0 | Fourth Address A1: A0 |
|----------------------|-----------------------|----------------------|-----------------------|
| 00                   | 01                    | 10                   | 11                    |
| 01                   | 10                    | 11                   | 00                    |
| 10                   | 11                    | 00                   | 01                    |
| 11                   | 00                    | 01                   | 10                    |

## Truth Table

The truth table for CY7C1471V25, CY7C1473V25, and CY7C1475V25 follows. [2, 3, 4, 5, 6, 7, 8]

| Operation                     | Address Used | $\overline{CE}_1$ | $CE_2$ | $\overline{CE}_3$ | ZZ | ADV/LD | $\overline{WE}$ | $\overline{BW}_x$ | $\overline{OE}$ | $\overline{CEN}$ | CLK  | DQ           |
|-------------------------------|--------------|-------------------|--------|-------------------|----|--------|-----------------|-------------------|-----------------|------------------|------|--------------|
| Deselect Cycle                | None         | H                 | X      | X                 | L  | L      | X               | X                 | X               | L                | L->H | Tri-State    |
| Deselect Cycle                | None         | X                 | X      | H                 | L  | L      | X               | X                 | X               | L                | L->H | Tri-State    |
| Deselect Cycle                | None         | X                 | L      | X                 | L  | L      | X               | X                 | X               | L                | L->H | Tri-State    |
| Continue Deselect Cycle       | None         | X                 | X      | X                 | L  | H      | X               | X                 | X               | L                | L->H | Tri-State    |
| Read Cycle (Begin Burst)      | External     | L                 | H      | L                 | L  | L      | H               | X                 | L               | L                | L->H | Data Out (Q) |
| Read Cycle (Continue Burst)   | Next         | X                 | X      | X                 | L  | H      | X               | X                 | L               | L                | L->H | Data Out (Q) |
| NOP/Dummy Read (Begin Burst)  | External     | L                 | H      | L                 | L  | L      | H               | X                 | H               | L                | L->H | Tri-State    |
| Dummy Read (Continue Burst)   | Next         | X                 | X      | X                 | L  | H      | X               | X                 | H               | L                | L->H | Tri-State    |
| Write Cycle (Begin Burst)     | External     | L                 | H      | L                 | L  | L      | L               | L                 | X               | L                | L->H | Data In (D)  |
| Write Cycle (Continue Burst)  | Next         | X                 | X      | X                 | L  | H      | X               | L                 | X               | L                | L->H | Data In (D)  |
| NOP/Write Abort (Begin Burst) | None         | L                 | H      | L                 | L  | L      | L               | H                 | X               | L                | L->H | Tri-State    |
| Write Abort (Continue Burst)  | Next         | X                 | X      | X                 | L  | H      | X               | H                 | X               | L                | L->H | Tri-State    |
| Ignore Clock Edge (Stall)     | Current      | X                 | X      | X                 | L  | X      | X               | X                 | X               | H                | L->H | -            |
| Sleep Mode                    | None         | X                 | X      | X                 | H  | X      | X               | X                 | X               | X                | X    | Tri-State    |

### Notes

- X = "Don't Care." H = Logic HIGH, L = Logic LOW.  $\overline{BW}_x = L$  signifies at least one Byte Write Select is active,  $\overline{BW}_x = \text{Valid}$  signifies that the desired Byte Write Selects are asserted, see "Truth Table for Read/Write" on page 12 for details.
- Write is defined by  $\overline{BW}_x$ , and  $\overline{WE}$ . See "Truth Table for Read/Write" on page 12.
- When a write cycle is detected, all IOs are tri-stated, even during byte writes.
- The DQs and  $DQP_x$  pins are controlled by the current cycle and the  $\overline{OE}$  signal.  $\overline{OE}$  is asynchronous and is not sampled with the clock.
- $\overline{CEN} = H$ , inserts wait states.
- Device powers up deselected with the IOs in a tri-state condition, regardless of  $\overline{OE}$ .
- $\overline{OE}$  is asynchronous and is not sampled with the clock rise. It is masked internally during write cycles. During a read cycle DQs and  $DQP_x = \text{tri-state}$  when  $\overline{OE}$  is inactive or when the device is deselected, and DQs and  $DQP_x = \text{data}$  when  $\overline{OE}$  is active.

### Truth Table for Read/Write

The read-write truth table for CY7C1471V25 follows.<sup>[2, 3, 9]</sup>

| Function   | $\overline{WE}$ | $\overline{BW}_A$ | $\overline{BW}_B$ | $\overline{BW}_C$ | $\overline{BW}_D$ |
|--|-----------------|-------------------|-------------------|-------------------|-------------------|
| Read   | H               | X                 | X                 | X                 | X                 |
| Write No bytes written                                 | L               | H                 | H                 | H                 | H                 |
| Write Byte A – (DQ <sub>A</sub> and DQP <sub>A</sub> ) | L               | L                 | H                 | H                 | H                 |
| Write Byte B – (DQ <sub>B</sub> and DQP <sub>B</sub> ) | L               | H                 | L                 | H                 | H                 |
| Write Byte C – (DQ <sub>C</sub> and DQP <sub>C</sub> ) | L               | H                 | H                 | L                 | H                 |
| Write Byte D – (DQ <sub>D</sub> and DQP <sub>D</sub> ) | L               | H                 | H                 | H                 | L                 |
| Write All Bytes  | L               | L                 | L                 | L                 | L                 |

### Truth Table for Read/Write

The read-write truth table for CY7C1473V25 follows.<sup>[2, 3, 9]</sup>

| Function   | $\overline{WE}$ | $\overline{BW}_b$ | $\overline{BW}_a$ |
|--|-----------------|-------------------|-------------------|
| Read   | H               | X                 | X                 |
| Write – No Bytes Written                               | L               | H                 | H                 |
| Write Byte a – (DQ <sub>a</sub> and DQP <sub>a</sub> ) | L               | H                 | L                 |
| Write Byte b – (DQ <sub>b</sub> and DQP <sub>b</sub> ) | L               | L                 | H                 |
| Write Both Bytes                                       | L               | L                 | L                 |

### Truth Table for Read/Write

The read-write truth table for CY7C1475V25 follows.<sup>[2, 3, 9]</sup>

| Function   | $\overline{WE}$ | $\overline{BW}_x$       |
|--|-----------------|-------------------------|
| Read   | H               | X                       |
| Write – No Bytes Written                               | L               | H                       |
| Write Byte X – (DQ <sub>x</sub> and DQP <sub>x</sub> ) | L               | L                       |
| Write All Bytes  | L               | All $\overline{BW} = L$ |

**Note**

9. Table lists only a partial listing of the byte write combinations. Any combination of  $\overline{BW}_x$  is valid. Appropriate write is based on which byte write is active.

## IEEE 1149.1 Serial Boundary Scan (JTAG)

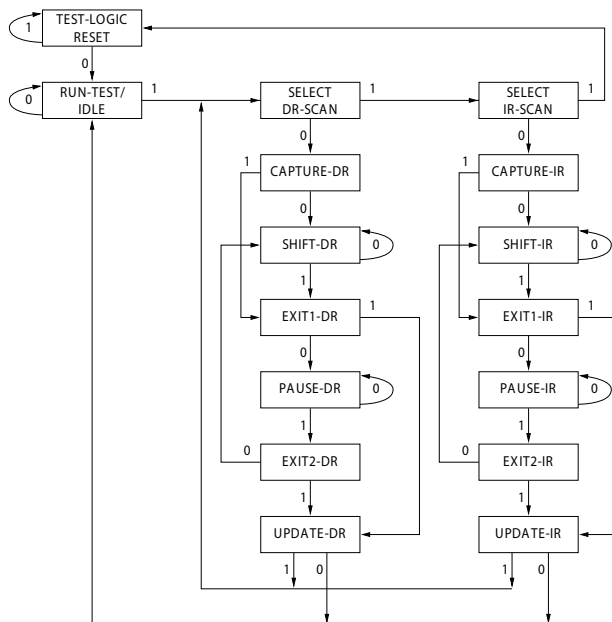
The CY7C1471V25, CY7C1473V25, and CY7C1475V25 and incorporate a serial boundary scan test access port (TAP). This port operates in accordance with IEEE Standard 1149.1-1990 but does not have the set of functions required for full 1149.1 compliance. These functions from the IEEE specification are excluded because their inclusion places an added delay in the critical speed path of the SRAM. Note that the TAP controller functions in a manner that does not conflict with the operation of other devices using 1149.1 fully compliant TAPs. The TAP operates using JEDEC-standard 2.5V or 1.8V IO logic levels.

The CY7C1471V25, CY7C1473V25, and CY7C1475V25 contain a TAP controller, instruction register, boundary scan register, bypass register, and ID register.

### Disabling the JTAG Feature

It is possible to operate the SRAM without using the JTAG feature. To disable the TAP controller, TCK must be tied LOW ( $V_{SS}$ ) to prevent clocking of the device. TDI and TMS are internally pulled up and may be unconnected. They may alternately be connected to  $V_{DD}$  through a pull up resistor. TDO must be left unconnected. During power up, the device comes up in a reset state, which does not interfere with the operation of the device.

### TAP Controller State Diagram



The 0/1 next to each state represents the value of TMS at the rising edge of TCK.

### Test Access Port (TAP)

#### Test Clock (TCK)

The test clock is used only with the TAP controller. All inputs are captured on the rising edge of TCK. All outputs are driven from the falling edge of TCK.

#### Test Mode Select (TMS)

The TMS input is used to give commands to the TAP controller and is sampled on the rising edge of TCK. It is allowable to leave this ball unconnected if the TAP is not used. The ball is pulled up internally, resulting in a logic HIGH level.

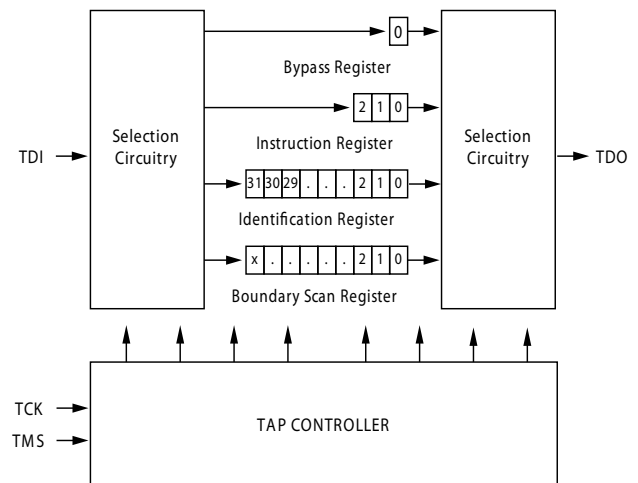
#### Test Data-In (TDI)

The TDI ball is used to serially input information into the registers and can be connected to the input of any of the registers. The register between TDI and TDO is chosen by the instruction that is loaded into the TAP instruction register. For information about loading the instruction register, see the [TAP Controller State Diagram](#). TDI is internally pulled up and can be unconnected if the TAP is unused in an application. TDI is connected to the most significant bit (MSB) of any register. (See [TAP Controller Block Diagram](#).)

#### Test Data-Out (TDO)

The TDO output ball is used to serially clock data-out from the registers. The output is active depending upon the current state of the TAP state machine. The output changes on the falling edge of TCK. TDO is connected to the least significant bit (LSB) of any register. (See [Tap Controller State Diagram](#).)

### TAP Controller Block Diagram



### Performing a TAP Reset

A RESET is performed by forcing TMS HIGH ( $V_{DD}$ ) for five rising edges of TCK. This RESET does not affect the operation of the SRAM and may be performed while the SRAM is operating.

During power up, the TAP is reset internally to ensure that TDO comes up in a High-Z state.

## TAP Registers

Registers are connected between the TDI and TDO balls and enable data to be scanned into and out of the SRAM test circuitry. Only one register can be selected at a time through the instruction register. Data is serially loaded into the TDI ball on the rising edge of TCK. Data is output on the TDO ball on the falling edge of TCK.

### *Instruction Register*

Three-bit instructions can be serially loaded into the instruction register. This register is loaded when it is placed between the TDI and TDO balls as shown in the [“TAP Controller Block Diagram” on page 13](#). During power up, the instruction register is loaded with the IDCODE instruction. It is also loaded with the IDCODE instruction if the controller is placed in a reset state as described in the previous section.

When the TAP controller is in the Capture-IR state, the two least significant bits are loaded with a binary ‘01’ pattern to enable fault isolation of the board-level serial test data path.

### *Bypass Register*

To save time when serially shifting data through registers, it is sometimes advantageous to skip certain chips. The bypass register is a single-bit register that can be placed between the TDI and TDO balls. This allows data to be shifted through the SRAM with minimal delay. The bypass register is set LOW ( $V_{SS}$ ) when the BYPASS instruction is executed.

### *Boundary Scan Register*

The boundary scan register is connected to all the input and bidirectional balls on the SRAM.

The boundary scan register is loaded with the contents of the RAM IO ring when the TAP controller is in the Capture-DR state and is then placed between the TDI and TDO balls when the controller is moved to the Shift-DR state. The EXTEST, SAMPLE/PRELOAD and SAMPLE Z instructions can be used to capture the contents of the IO ring.

The Boundary Scan Order tables show the order in which the bits are connected. Each bit corresponds to one of the bumps on the SRAM package. The MSB of the register is connected to TDI and the LSB is connected to TDO.

### *Identification (ID) Register*

The ID register is loaded with a vendor-specific, 32-bit code during the Capture-DR state when the IDCODE command is loaded in the instruction register. The IDCODE is hardwired into the SRAM and can be shifted out when the TAP controller is in the Shift-DR state. The ID register has a vendor code and other information described in [“Identification Register Definitions” on page 17](#).

## TAP Instruction Set

### *Overview*

Eight different instructions are possible with the three-bit instruction register. All combinations are listed in [“Identification Codes” on page 18](#). Three of these instructions are listed as RESERVED and must not be used. The other five instructions are described in this section in detail.

The TAP controller used in this SRAM is not fully compliant to the 1149.1 convention because some of the mandatory 1149.1 instructions are not fully implemented.

The TAP controller cannot be used to load address data or control signals into the SRAM and cannot preload the IO buffers. The SRAM does not implement the 1149.1 commands EXTEST or INTEST or the PRELOAD portion of SAMPLE/PRELOAD; rather, it performs a capture of the IO ring when these instructions are executed.

Instructions are loaded into the TAP controller during the Shift-IR state when the instruction register is placed between TDI and TDO. During this state, instructions are shifted through the instruction register through the TDI and TDO balls. To execute the instruction after it is shifted in, the TAP controller needs to be moved into the Update-IR state.

### *EXTEST*

EXTEST is a mandatory 1149.1 instruction which is to be executed whenever the instruction register is loaded with all 0s. EXTEST is not implemented in this SRAM TAP controller, and therefore this device is not compliant to 1149.1. The TAP controller does not recognize an all-0 instruction.

When an EXTEST instruction is loaded into the instruction register, the SRAM responds as if a SAMPLE/PRELOAD instruction has been loaded. There is one difference between the two instructions. Unlike the SAMPLE/PRELOAD instruction, EXTEST places the SRAM outputs in a High-Z state.

### *IDCODE*

The IDCODE instruction causes a vendor-specific, 32-bit code to be loaded into the instruction register. It also places the instruction register between the TDI and TDO balls and enables the IDCODE to be shifted out of the device when the TAP controller enters the Shift-DR state.

The IDCODE instruction is loaded into the instruction register during power up or whenever the TAP controller is in a test logic reset state.

### *SAMPLE Z*

The SAMPLE Z instruction causes the boundary scan register to be connected between the TDI and TDO balls when the TAP controller is in a Shift-DR state. It also places all SRAM outputs into a High-Z state.

### *SAMPLE/PRELOAD*

SAMPLE/PRELOAD is a 1149.1 mandatory instruction. The PRELOAD portion of this instruction is not implemented, so the device TAP controller is not fully 1149.1 compliant.

When the SAMPLE/PRELOAD instruction is loaded into the instruction register and the TAP controller is in the Capture-DR state, a snapshot of data on the inputs and bidirectional balls is captured in the boundary scan register.

The user must be aware that the TAP controller clock can only operate at a frequency up to 20 MHz, while the SRAM clock operates more than an order of magnitude faster. Because there is a large difference in the clock frequencies, it is possible that during the Capture-DR state, an input or output may undergo a transition. The TAP may then try to capture a

signal while in transition (metastable state). This does not harm the device, but there is no guarantee as to the value that is captured. Repeatable results may not be possible.

To guarantee that the boundary scan register captures the correct value of a signal, the SRAM signal must be stabilized long enough to meet the TAP controller's capture setup plus hold time ( $t_{CS}$  plus  $t_{CH}$ ).

The SRAM clock input might not be captured correctly if there is no way in a design to stop (or slow) the clock during a SAMPLE/PRELOAD instruction. If this is an issue, it is still possible to capture all other signals and simply ignore the value of the CLK captured in the boundary scan register.

After the data is captured, it is possible to shift out the data by putting the TAP into the Shift-DR state. This places the boundary scan register between the TDI and TDO balls.

Note that since the PRELOAD part of the command is not implemented, putting the TAP to the Update-DR state while performing a SAMPLE/PRELOAD instruction has the same effect as the Pause-DR command.

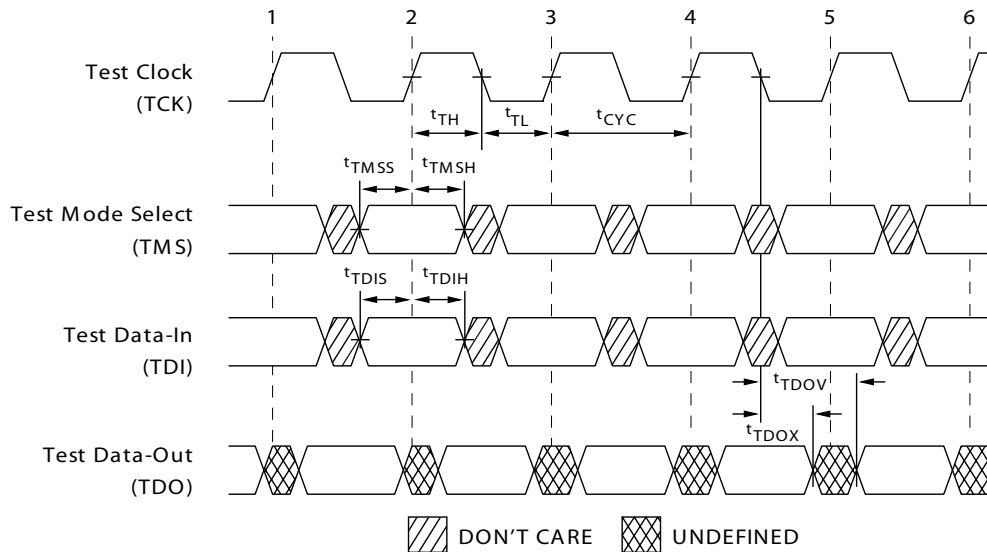
**BYPASS**

When the BYPASS instruction is loaded in the instruction register and the TAP is placed in a Shift-DR state, the bypass register is placed between the TDI and TDO balls. The advantage of the BYPASS instruction is that it shortens the boundary scan path when multiple devices are connected together on a board.

**Reserved**

These instructions are not implemented but are reserved for future use. Do not use these instructions.

**TAP Timing**



## TAP AC Switching Characteristics

Over the Operating Range<sup>[10, 11]</sup>

| Parameter           | Description                   | Min | Max | Unit |
|---------------------|-------------------------------|-----|-----|------|
| <b>Clock</b>        |                               |     |     |      |
| t <sub>TCYC</sub>   | TCK Clock Cycle Time          | 50  |     | ns   |
| t <sub>TF</sub>     | TCK Clock Frequency           |     | 20  | MHz  |
| t <sub>TH</sub>     | TCK Clock HIGH Time           | 20  |     | ns   |
| t <sub>TL</sub>     | TCK Clock LOW Time            | 20  |     | ns   |
| <b>Output Times</b> |                               |     |     |      |
| t <sub>TDOV</sub>   | TCK Clock LOW to TDO Valid    |     | 10  | ns   |
| t <sub>TDOX</sub>   | TCK Clock LOW to TDO Invalid  | 0   |     | ns   |
| <b>Setup Times</b>  |                               |     |     |      |
| t <sub>TMSS</sub>   | TMS Setup to TCK Clock Rise   | 5   |     | ns   |
| t <sub>TDIS</sub>   | TDI Setup to TCK Clock Rise   | 5   |     | ns   |
| t <sub>CS</sub>     | Capture Setup to TCK Rise     | 5   |     | ns   |
| <b>Hold Times</b>   |                               |     |     |      |
| t <sub>TMSH</sub>   | TMS Hold after TCK Clock Rise | 5   |     | ns   |
| t <sub>TDIH</sub>   | TDI Hold after Clock Rise     | 5   |     | ns   |
| t <sub>CH</sub>     | Capture Hold after Clock Rise | 5   |     | ns   |

### Notes

10. t<sub>CS</sub> and t<sub>CH</sub> refer to the setup and hold time requirements of latching data from the boundary scan register.

11. Test conditions are specified using the load in TAP AC Test Conditions. t<sub>r</sub>/t<sub>f</sub> = 1 ns.



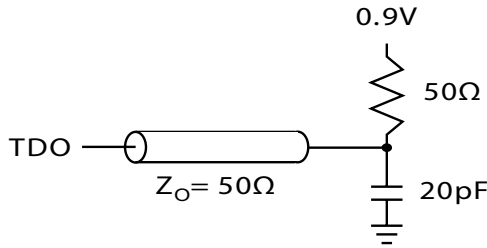
### 1.8V TAP AC Test Conditions

Input pulse levels ..... 0.2V to  $V_{DDQ} - 0.2$   
 Input rise and fall time ..... 1 ns  
 Input timing reference levels ..... 0.9V  
 Output reference levels ..... 0.9V  
 Test load termination supply voltage ..... 0.9V

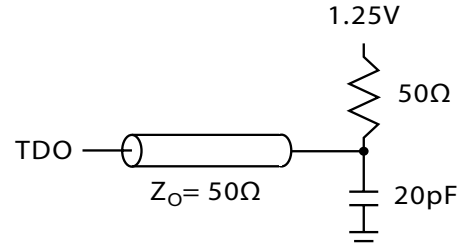
### 2.5V TAP AC Test Conditions

Input pulse levels .....  $V_{SS}$  to 2.5V  
 Input rise and fall time ..... 1 ns  
 Input timing reference levels ..... 1.25V  
 Output reference levels ..... 1.25V  
 Test load termination supply voltage ..... 1.25V

### 1.8V TAP AC Output Load Equivalent



### 2.5V TAP AC Output Load Equivalent



### TAP DC Electrical Characteristics And Operating Conditions

( $0^{\circ}\text{C} < T_A < +70^{\circ}\text{C}$ ;  $V_{DD} = 2.375$  to  $2.625$  unless otherwise noted)<sup>[12]</sup>

| Parameter | Description         | Test Conditions                       | Min.              | Max. | Unit           |   |
|-----------|---------------------|---------------------------------------|-------------------|------|----------------|---|
| $V_{OH1}$ | Output HIGH Voltage | $I_{OH} = -1.0$ mA, $V_{DDQ} = 2.5$ V | 2.0               |      | V              |   |
| $V_{OH2}$ | Output HIGH Voltage | $I_{OH} = -100$ $\mu$ A               | $V_{DDQ} = 2.5$ V | 2.1  | V              |   |
|           |                     |                                       | $V_{DDQ} = 1.8$ V | 1.6  | V              |   |
| $V_{OL1}$ | Output LOW Voltage  | $I_{OL} = 1.0$ mA, $V_{DDQ} = 2.5$ V  |                   | 0.4  | V              |   |
| $V_{OL2}$ | Output LOW Voltage  | $I_{OL} = 100$ $\mu$ A                | $V_{DDQ} = 2.5$ V |      | 0.2            | V |
|           |                     |                                       | $V_{DDQ} = 1.8$ V |      | 0.2            | V |
| $V_{IH}$  | Input HIGH Voltage  |                                       | $V_{DDQ} = 2.5$ V | 1.7  | $V_{DD} + 0.3$ | V |
|           |                     |                                       | $V_{DDQ} = 1.8$ V | 1.26 | $V_{DD} + 0.3$ | V |
| $V_{IL}$  | Input LOW Voltage   |                                       | $V_{DDQ} = 2.5$ V | -0.3 | 0.7            | V |
|           |                     |                                       | $V_{DDQ} = 1.8$ V | -0.3 | 0.36           | V |
| $I_X$     | Input Load Current  | $GND \leq V_{IN} \leq V_{DDQ}$        | -5                | 5    | $\mu$ A        |   |

### Identification Register Definitions

| Instruction Field                  | CY7C1471V25 (2MX36) | CY7C1473V25 (4MX18) | CY7C1475V25 (1MX72) | Description                                 |
|------------------------------------|---------------------|---------------------|---------------------|---|
| Revision Number (31:29)            | 000                 | 000                 | 000                 | Describes the version number                |
| Device Depth (28:24)               | 01011               | 01011               | 01011               | Reserved for internal use                   |
| Architecture/Memory Type(23:18)    | 001001              | 001001              | 001001              | Defines memory type and architecture        |
| Bus Width/Density(17:12)           | 100100              | 010100              | 110100              | Defines width and density                   |
| Cypress JEDEC ID Code (11:1)       | 00000110100         | 00000110100         | 00000110100         | Allows unique identification of SRAM vendor |
| ID Register Presence Indicator (0) | 1                   | 1                   | 1                   | Indicates the presence of an ID register    |

**Note**

12. All voltages refer to  $V_{SS}$  (GND).

### Scan Register Sizes

| Register Name                 | Bit Size (x36) | Bit Size (x18) | Bit Size (x72) |
|-------------------------------|----------------|----------------|----------------|
| Instruction                   | 3              | 3              | 3              |
| Bypass                        | 1              | 1              | 1              |
| ID                            | 32             | 32             | 32             |
| Boundary Scan Order – 165FBGA | 71             | 52             | -              |
| Boundary Scan Order – 209BGA  | -              | -              | 110            |

### Identification Codes

| Instruction    | Code | Description  |
|----------------|------|--|
| EXTEST         | 000  | Captures IO ring contents. Places the boundary scan register between TDI and TDO. Forces all SRAM outputs to High-Z state. This instruction is not 1149.1 compliant.   |
| IDCODE         | 001  | Loads the ID register with the vendor ID code and places the register between TDI and TDO. This operation does not affect SRAM operations.   |
| SAMPLE Z       | 010  | Captures IO ring contents. Places the boundary scan register between TDI and TDO. Forces all SRAM output drivers to a High-Z state.  |
| RESERVED       | 011  | Do Not Use: This instruction is reserved for future use.   |
| SAMPLE/PRELOAD | 100  | Captures IO ring contents. Places the boundary scan register between TDI and TDO. Does not affect SRAM operation. This instruction does not implement 1149.1 preload function and is therefore not 1149.1 compliant. |
| RESERVED       | 101  | Do Not Use: This instruction is reserved for future use.   |
| RESERVED       | 110  | Do Not Use: This instruction is reserved for future use.   |
| BYPASS         | 111  | Places the bypass register between TDI and TDO. This operation does not affect SRAM operation.   |



**Boundary Scan Exit Order (1M x 72)**

| Bit # | 209-Ball ID |
|-------|-------------|
| 1     | A1          |
| 2     | A2          |
| 3     | B1          |
| 4     | B2          |
| 5     | C1          |
| 6     | C2          |
| 7     | D1          |
| 8     | D2          |
| 9     | E1          |
| 10    | E2          |
| 11    | F1          |
| 12    | F2          |
| 13    | G1          |
| 14    | G2          |
| 15    | H1          |
| 16    | H2          |
| 17    | J1          |
| 18    | J2          |
| 19    | L1          |
| 20    | L2          |
| 21    | M1          |
| 22    | M2          |
| 23    | N1          |
| 24    | N2          |
| 25    | P1          |
| 26    | P2          |
| 27    | R2          |
| 28    | R1          |

| Bit # | 209-Ball ID |
|-------|-------------|
| 29    | T1          |
| 30    | T2          |
| 31    | U1          |
| 32    | U2          |
| 33    | V1          |
| 34    | V2          |
| 35    | W1          |
| 36    | W2          |
| 37    | T6          |
| 38    | V3          |
| 39    | V4          |
| 40    | U4          |
| 41    | W5          |
| 42    | V6          |
| 43    | W6          |
| 44    | V5          |
| 45    | U5          |
| 46    | U6          |
| 47    | W7          |
| 48    | V7          |
| 49    | U7          |
| 50    | V8          |
| 51    | V9          |
| 52    | W11         |
| 53    | W10         |
| 54    | V11         |
| 55    | V10         |
| 56    | U11         |

| Bit # | 209-Ball ID |
|-------|-------------|
| 57    | U10         |
| 58    | T11         |
| 59    | T10         |
| 60    | R11         |
| 61    | R10         |
| 62    | P11         |
| 63    | P10         |
| 64    | N11         |
| 65    | N10         |
| 66    | M11         |
| 67    | M10         |
| 68    | L11         |
| 69    | L10         |
| 70    | P6          |
| 71    | J11         |
| 72    | J10         |
| 73    | H11         |
| 74    | H10         |
| 75    | G11         |
| 76    | G10         |
| 77    | F11         |
| 78    | F10         |
| 79    | E10         |
| 80    | E11         |
| 81    | D11         |
| 82    | D10         |
| 83    | C11         |
| 84    | C10         |

| Bit # | 209-Ball ID |
|-------|-------------|
| 85    | B11         |
| 86    | B10         |
| 87    | A11         |
| 88    | A10         |
| 89    | A7          |
| 90    | A5          |
| 91    | A9          |
| 92    | U8          |
| 93    | A6          |
| 94    | D6          |
| 95    | K6          |
| 96    | B6          |
| 97    | K3          |
| 98    | A8          |
| 99    | B4          |
| 100   | B3          |
| 101   | C3          |
| 102   | C4          |
| 103   | C8          |
| 104   | C9          |
| 105   | B9          |
| 106   | B8          |
| 107   | A4          |
| 108   | C6          |
| 109   | B7          |
| 110   | A3          |
|       |             |
|       |             |

## Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature ..... -65°C to +150°C  
 Ambient Temperature with Power Applied ..... -55°C to +125°C  
 Supply Voltage on V<sub>DD</sub> Relative to GND ..... -0.5V to +3.6V  
 Supply Voltage on V<sub>DDQ</sub> Relative to GND ..... -0.5V to +V<sub>DD</sub>  
 DC Voltage Applied to Outputs in Tri-State ..... -0.5V to V<sub>DDQ</sub> + 0.5V

DC Input Voltage ..... -0.5V to V<sub>DD</sub> + 0.5V  
 Current into Outputs (LOW) ..... 20 mA  
 Static Discharge Voltage ..... >2001V (MIL-STD-883, Method 3015)  
 Latch Up Current ..... >200 mA

## Operating Range

| Range      | Ambient Temperature | V <sub>DD</sub> | V <sub>DDQ</sub>        |
|------------|---------------------|-----------------|-------------------------|
| Commercial | 0°C to +70°C        | 2.5V-5%/+5%     | 1.7V to V <sub>DD</sub> |
| Industrial | -40°C to +85°C      |                 |                         |

## Electrical Characteristics

Over the Operating Range <sup>[13, 14]</sup>

| Parameter               | Description                                 | Test Conditions  | Min                   | Max                    | Unit |
|-------------------------|---|--|-----------------------|------------------------|------|
| V <sub>DD</sub>         | Power Supply Voltage                        |  | 2.375                 | 2.625                  | V    |
| V <sub>DDQ</sub>        | IO Supply Voltage                           | For 2.5V IO  | 2.375                 | V <sub>DD</sub>        | V    |
|                         |   | For 1.8V IO  | 1.7                   | 1.9                    | V    |
| V <sub>OH</sub>         | Output HIGH Voltage                         | For 2.5V IO, I <sub>OH</sub> = -1.0 mA   | 2.0                   |                        | V    |
|                         |   | For 1.8V IO, I <sub>OH</sub> = -100 μA   | 1.6                   |                        | V    |
| V <sub>OL</sub>         | Output LOW Voltage                          | For 2.5V IO, I <sub>OL</sub> = 1.0 mA  |                       | 0.4                    | V    |
|                         |   | For 1.8V IO, I <sub>OL</sub> = 100 μA,   |                       | 0.2                    | V    |
| V <sub>IH</sub>         | Input HIGH Voltage <sup>[13]</sup>          | For 2.5V IO  | 1.7                   | V <sub>DD</sub> + 0.3V | V    |
|                         |   | For 1.8V IO  | 1.26                  | V <sub>DD</sub> + 0.3V | V    |
| V <sub>IL</sub>         | Input LOW Voltage <sup>[13]</sup>           | For 2.5V IO  | -0.3                  | 0.7                    | V    |
|                         |   | For 1.8V IO  | -0.3                  | 0.36                   | V    |
| I <sub>X</sub>          | Input Leakage Current except ZZ and MODE    | GND ≤ V <sub>I</sub> ≤ V <sub>DDQ</sub>  | -5                    | 5                      | μA   |
|                         | Input Current of MODE                       | Input = V <sub>SS</sub>  | -30                   |                        | μA   |
|                         |   | Input = V <sub>DD</sub>  |                       | 5                      | μA   |
|                         | Input Current of ZZ                         | Input = V <sub>SS</sub>  | -5                    |                        | μA   |
| Input = V <sub>DD</sub> |   |  | 30                    | μA                     |      |
| I <sub>OZ</sub>         | Output Leakage Current                      | GND ≤ V <sub>I</sub> ≤ V <sub>DDQ</sub> , Output Disabled  | -5                    | 5                      | μA   |
| I <sub>DD</sub>         | V <sub>DD</sub> Operating Supply Current    | V <sub>DD</sub> = Max., I <sub>OUT</sub> = 0 mA, f = f <sub>MAX</sub> = 1/t <sub>CYC</sub>   | 6.5 ns cycle, 133 MHz | 305                    | mA   |
|                         |   |  | 8.5 ns cycle, 100 MHz | 275                    | mA   |
| I <sub>SB1</sub>        | Automatic CE Power Down Current—TTL Inputs  | V <sub>DD</sub> = Max, Device Deselected, V <sub>IN</sub> ≥ V <sub>IH</sub> or V <sub>IN</sub> ≤ V <sub>IL</sub> , f = f <sub>MAX</sub> , inputs switching | 6.5 ns cycle, 133 MHz | 170                    | mA   |
|                         |   |  | 8.5 ns cycle, 100 MHz | 170                    | mA   |
| I <sub>SB2</sub>        | Automatic CE Power Down Current—CMOS Inputs | V <sub>DD</sub> = Max, Device Deselected, V <sub>IN</sub> ≤ 0.3V or V <sub>IN</sub> ≥ V <sub>DD</sub> - 0.3V, f = 0, inputs static                         | All speeds            | 120                    | mA   |
| I <sub>SB3</sub>        | Automatic CE Power Down Current—CMOS Inputs | V <sub>DD</sub> = Max, Device Deselected, or V <sub>IN</sub> ≤ 0.3V or V <sub>IN</sub> ≥ V <sub>DDQ</sub> - 0.3V, f = f <sub>MAX</sub> , inputs switching  | 6.5 ns cycle, 133 MHz | 170                    | mA   |
|                         |   |  | 8.5 ns cycle, 100 MHz | 170                    | mA   |
| I <sub>SB4</sub>        | Automatic CE Power Down Current—TTL Inputs  | V <sub>DD</sub> = Max, Device Deselected, V <sub>IN</sub> ≥ V <sub>DD</sub> - 0.3V or V <sub>IN</sub> ≤ 0.3V, f = 0, inputs static                         | All Speeds            | 135                    | mA   |

### Notes

13. Overshoot: V<sub>IH</sub>(AC) < V<sub>DD</sub> + 1.5V (pulse width less than t<sub>CYC</sub>/2). Undershoot: V<sub>IL</sub>(AC) > -2V (pulse width less than t<sub>CYC</sub>/2).

14. T<sub>Power-up</sub>: assumes a linear ramp from 0V to V<sub>DD</sub>(min.) within 200 ms. During this time V<sub>IH</sub> < V<sub>DD</sub> and V<sub>DDQ</sub> ≤ V<sub>DD</sub>.

## Capacitance

Tested initially and after any design or process change that may affect these parameters.

| Parameter     | Description               | Test Conditions  | 100 TQFP Max. | 165 FBGA Max. | 209 FBGA Max. | Unit |
|---------------|---------------------------|--|---------------|---------------|---------------|------|
| $C_{ADDRESS}$ | Address Input Capacitance | $T_A = 25^\circ\text{C}$ , $f = 1\text{ MHz}$ ,<br>$V_{DD} = 2.5\text{V}$<br>$V_{DDQ} = 2.5\text{V}$ | 6             | 6             | 6             | pF   |
| $C_{DATA}$    | Data Input Capacitance    |  | 5             | 5             | 5             | pF   |
| $C_{CTRL}$    | Control Input Capacitance |  | 8             | 8             | 8             | pF   |
| $C_{CLK}$     | Clock Input Capacitance   |  | 6             | 6             | 6             | pF   |
| $C_{IO}$      | Input-Output Capacitance  |  | 5             | 5             | 5             | pF   |

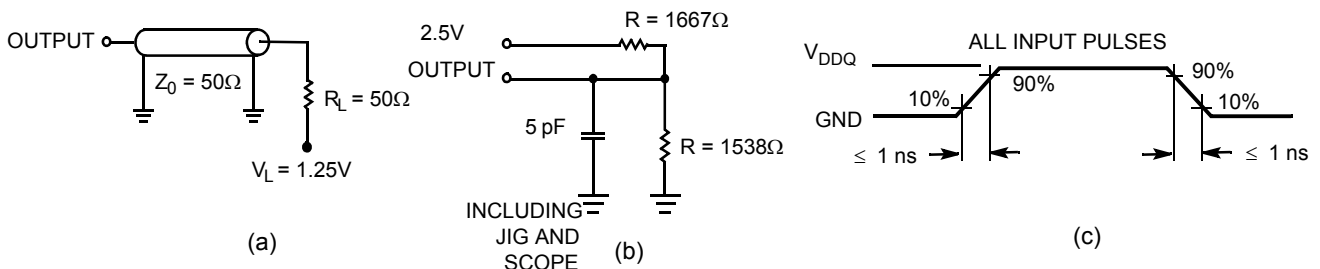
## Thermal Resistance

Tested initially and after any design or process change that may affect these parameters.

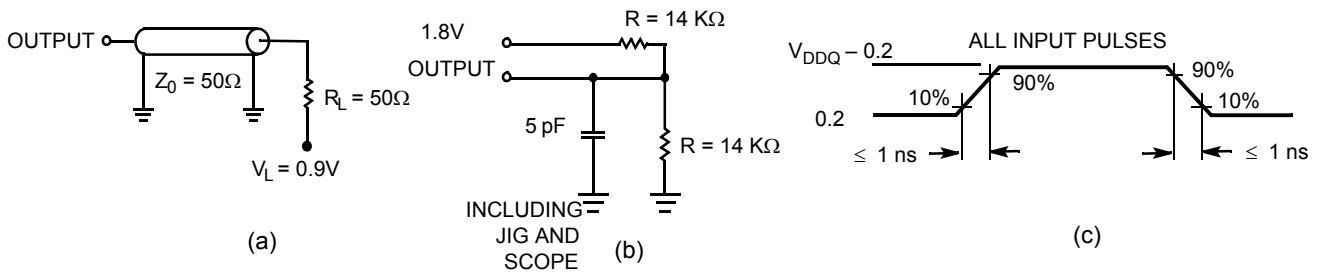
| Parameter     | Description                              | Test Conditions   | 100 TQFP Package | 165 FBGA Package | 209 FBGA Package | Unit               |
|---------------|--|---|------------------|------------------|------------------|--------------------|
| $\Theta_{JA}$ | Thermal Resistance (Junction to Ambient) | Test conditions follow standard test methods and procedures for measuring thermal impedance, according to EIA/JESD51. | 24.63            | 16.3             | 15.2             | $^\circ\text{C/W}$ |
| $\Theta_{JC}$ | Thermal Resistance (Junction to Case)    |   | 2.28             | 2.1              | 1.7              | $^\circ\text{C/W}$ |

## AC Test Loads and Waveforms

### 2.5V IO Test Load



### 1.8V IO Test Load



## Switching Characteristics

Over the Operating Range. Timing reference level is 1.25V when  $V_{DDQ} = 2.5V$  and is 0.9V when  $V_{DDQ} = 1.8V$ . Test conditions shown in (a) of “AC Test Loads and Waveforms” on page 22 unless otherwise noted.

| Parameter           | Description   | 133 MHz |     | 100 MHz |     | Unit |
|---------------------|---|---------|-----|---------|-----|------|
|                     |   | Min     | Max | Min     | Max |      |
| $t_{POWER}$         |   | 1       |     | 1       |     | ms   |
| <b>Clock</b>        |   |         |     |         |     |      |
| $t_{CYC}$           | Clock Cycle Time  | 7.5     |     | 10      |     | ns   |
| $t_{CH}$            | Clock HIGH  | 2.5     |     | 3.0     |     | ns   |
| $t_{CL}$            | Clock LOW   | 2.5     |     | 3.0     |     | ns   |
| <b>Output Times</b> |   |         |     |         |     |      |
| $t_{CDV}$           | Data Output Valid After CLK Rise                          |         | 6.5 |         | 8.5 | ns   |
| $t_{DOH}$           | Data Output Hold After CLK Rise                           | 2.5     |     | 2.5     |     | ns   |
| $t_{CLZ}$           | Clock to Low-Z [16, 17, 18]                               | 3.0     |     | 3.0     |     | ns   |
| $t_{CHZ}$           | Clock to High-Z [16, 17, 18]                              |         | 3.8 |         | 4.5 | ns   |
| $t_{OEV}$           | $\overline{OE}$ LOW to Output Valid                       |         | 3.0 |         | 3.8 | ns   |
| $t_{OELZ}$          | $\overline{OE}$ LOW to Output Low-Z [16, 17, 18]          | 0       |     | 0       |     | ns   |
| $t_{OEZH}$          | $\overline{OE}$ HIGH to Output High-Z [16, 17, 18]        |         | 3.0 |         | 4.0 | ns   |
| <b>Setup Times</b>  |   |         |     |         |     |      |
| $t_{AS}$            | Address Setup Before CLK Rise                             | 1.5     |     | 1.5     |     | ns   |
| $t_{ALS}$           | ADV/LD Setup Before CLK Rise                              | 1.5     |     | 1.5     |     | ns   |
| $t_{WES}$           | $\overline{WE}$ , $\overline{BW}_X$ Setup Before CLK Rise | 1.5     |     | 1.5     |     | ns   |
| $t_{CENS}$          | $\overline{CEN}$ Setup Before CLK Rise                    | 1.5     |     | 1.5     |     | ns   |
| $t_{DS}$            | Data Input Setup Before CLK Rise                          | 1.5     |     | 1.5     |     | ns   |
| $t_{CES}$           | Chip Enable Setup Before CLK Rise                         | 1.5     |     | 1.5     |     | ns   |
| <b>Hold Times</b>   |   |         |     |         |     |      |
| $t_{AH}$            | Address Hold After CLK Rise                               | 0.5     |     | 0.5     |     | ns   |
| $t_{ALH}$           | ADV/LD Hold After CLK Rise                                | 0.5     |     | 0.5     |     | ns   |
| $t_{WEH}$           | $\overline{WE}$ , $\overline{BW}_X$ Hold After CLK Rise   | 0.5     |     | 0.5     |     | ns   |
| $t_{CENH}$          | $\overline{CEN}$ Hold After CLK Rise                      | 0.5     |     | 0.5     |     | ns   |
| $t_{DH}$            | Data Input Hold After CLK Rise                            | 0.5     |     | 0.5     |     | ns   |
| $t_{CEH}$           | Chip Enable Hold After CLK Rise                           | 0.5     |     | 0.5     |     | ns   |

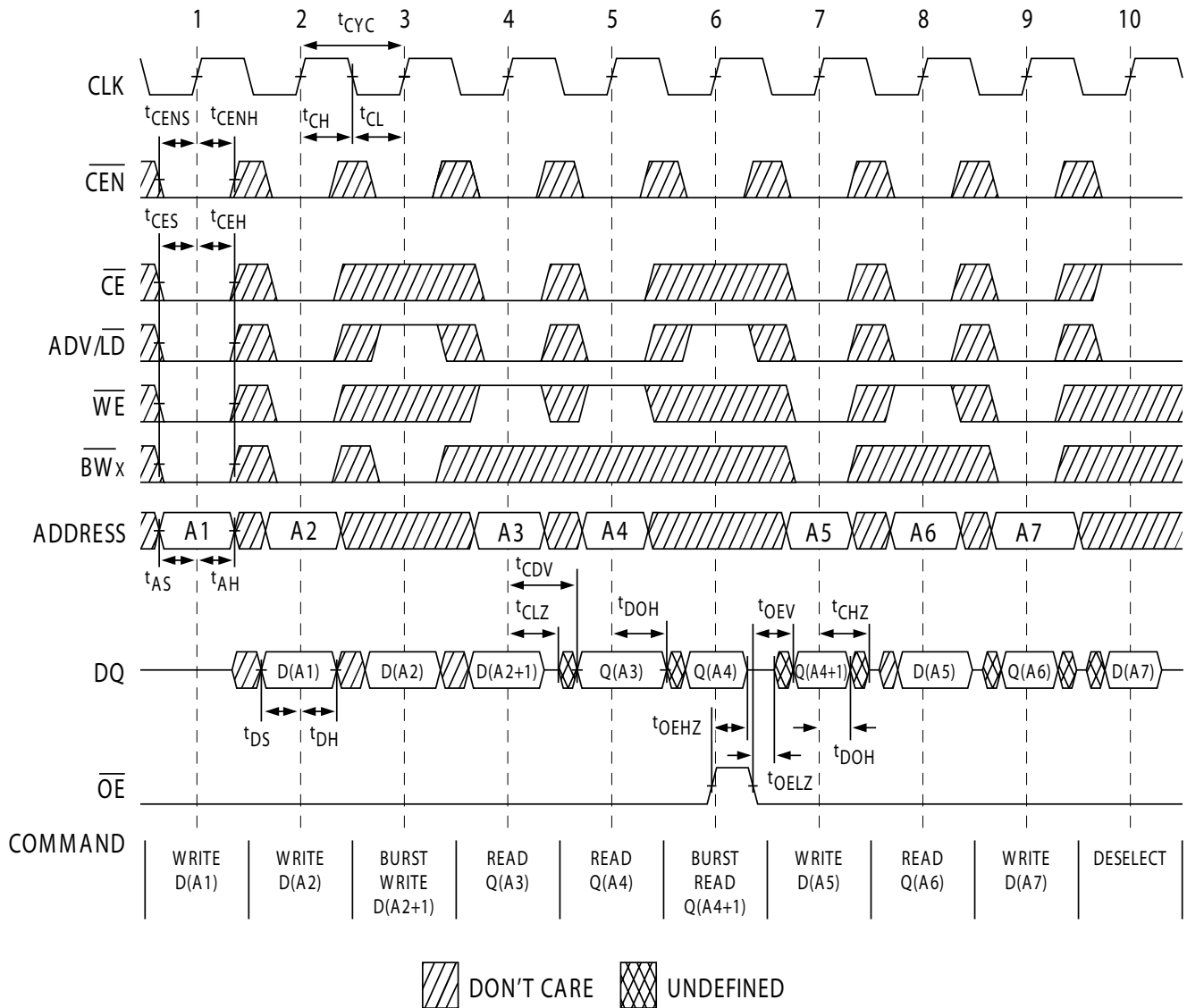
### Notes

15. This part has a voltage regulator internally;  $t_{POWER}$  is the time that the power needs to be supplied above  $V_{DD}$  (minimum) initially, before a read or write operation can be initiated.
16.  $t_{CHZ}$ ,  $t_{CLZ}$ ,  $t_{OELZ}$ , and  $t_{OEZH}$  are specified with AC test conditions shown in part (b) of “AC Test Loads and Waveforms” on page 22. Transition is measured  $\pm 200$  mV from steady-state voltage.
17. At any supplied voltage and temperature,  $t_{OEZH}$  is less than  $t_{OELZ}$  and  $t_{CHZ}$  is less than  $t_{CLZ}$  to eliminate bus contention between SRAMs when sharing the same data bus. These specifications do not imply a bus contention condition, but reflect parameters guaranteed over worst case user conditions. Device is designed to achieve High-Z before Low-Z under the same system conditions.
18. This parameter is sampled and not 100% tested.

## Switching Waveforms

Figure 1 shows read-write timing waveform. [19, 20, 21]

Figure 1. Read/Write Timing



### Notes

19. For this waveform ZZ is tied LOW.

20. When  $\overline{CE}$  is LOW,  $\overline{CE}_1$  is LOW,  $\overline{CE}_2$  is HIGH, and  $\overline{CE}_3$  is LOW. When  $\overline{CE}$  is HIGH,  $\overline{CE}_1$  is HIGH,  $\overline{CE}_2$  is LOW or  $\overline{CE}_3$  is HIGH.

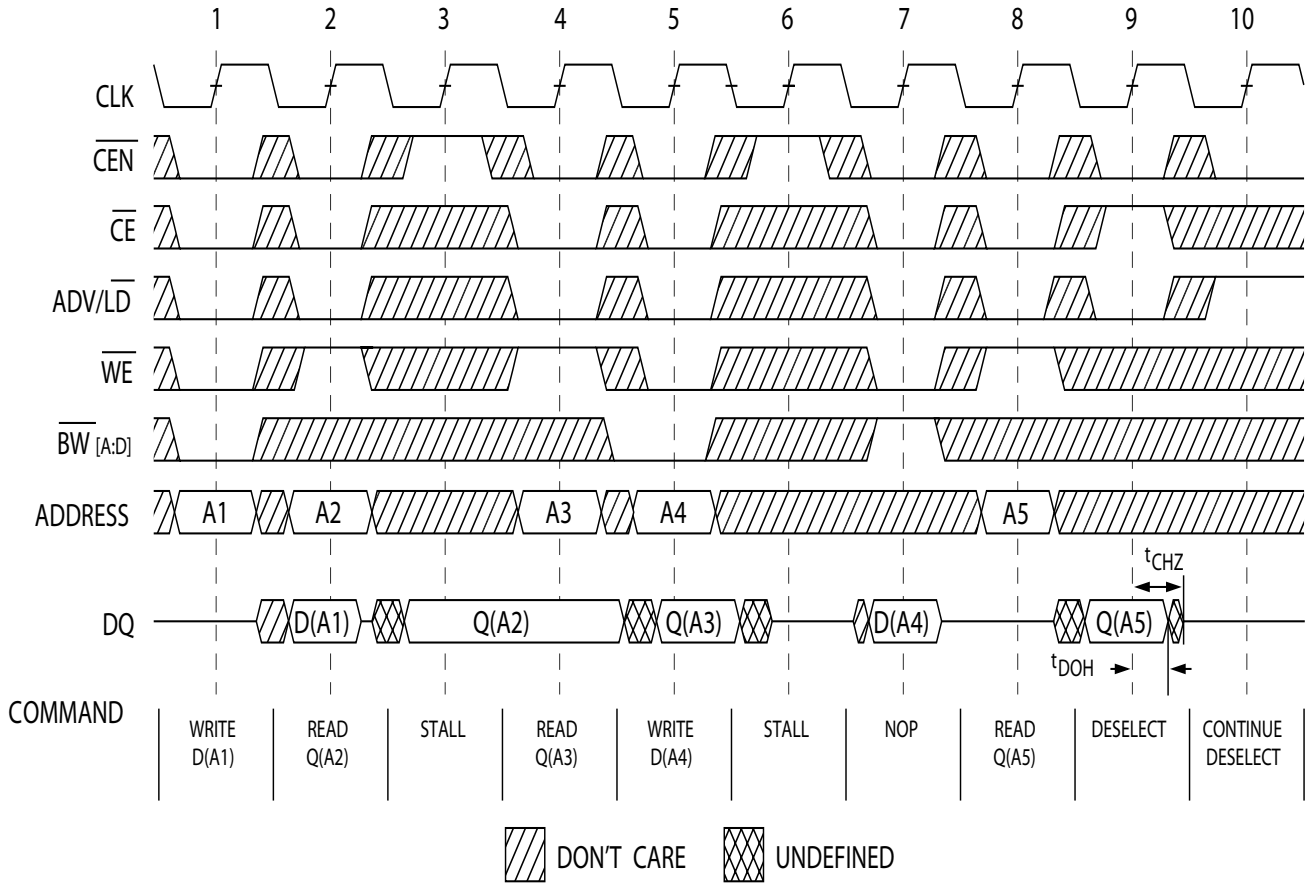
21. Order of the Burst sequence is determined by the status of the MODE (0 = Linear, 1 = Interleaved). Burst operations are optional.



**Switching Waveforms** (continued)

Figure 2 shows NOP, STALL and DESELECT Cycles waveform.<sup>[19, 20, 22]</sup>

**Figure 2. NOP, STALL and DESELECT Cycles**



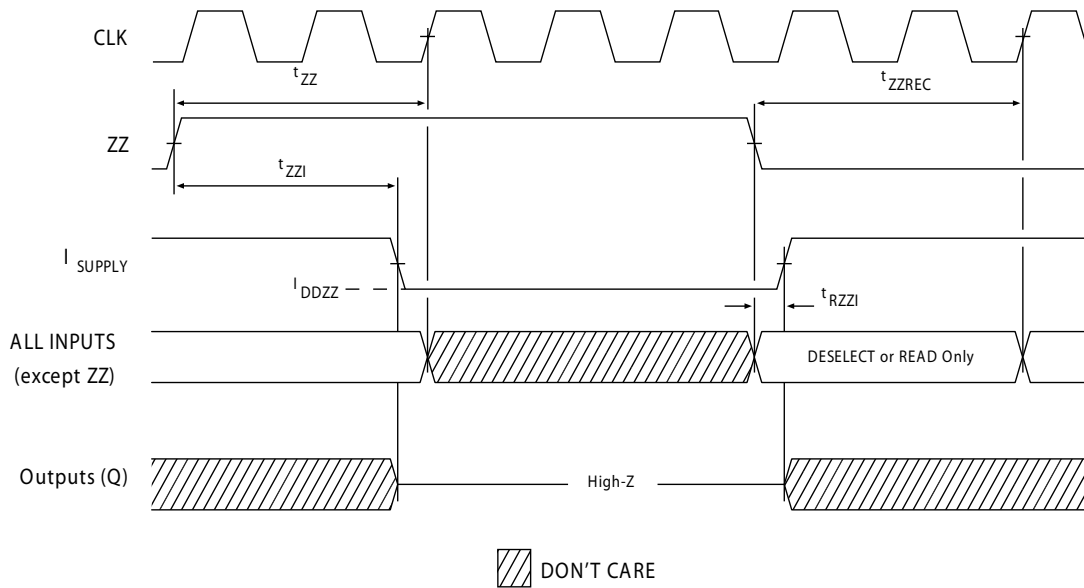
**Note**

22. The IGNORE CLOCK EDGE or STALL cycle (Clock 3) illustrates  $\overline{CEN}$  being used to create a pause. A write is not performed during this cycle.

**Switching Waveforms** (continued)

Figure 3 shows ZZ Mode timing waveform.<sup>[23, 24]</sup>

**Figure 3. ZZ Mode Timing**



**Notes**

- 23. Device must be deselected when entering ZZ mode. See "Truth Table" on page 11 for all possible signal conditions to deselect the device.
- 24. DQs are in high-Z when exiting ZZ sleep mode.

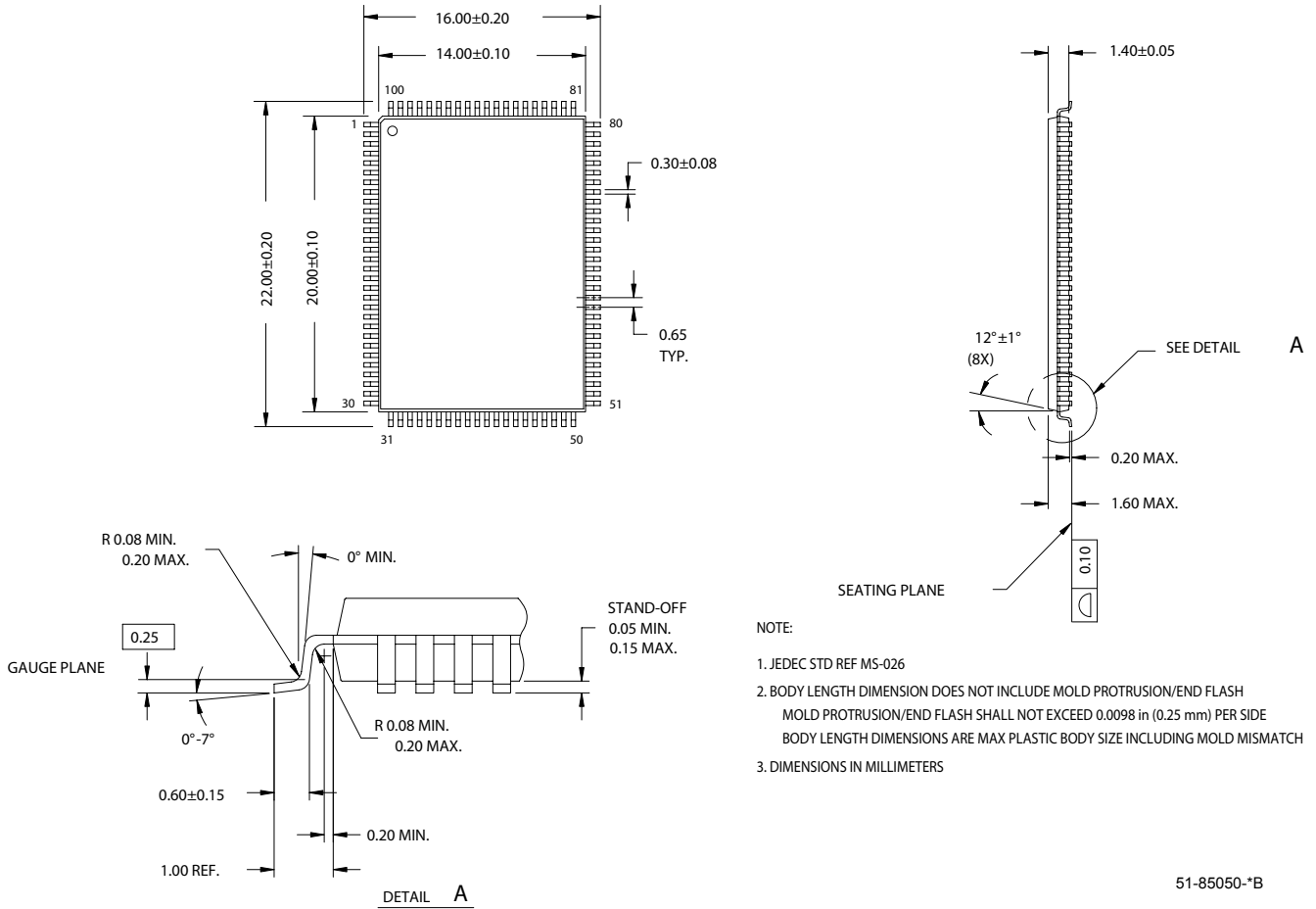
### Ordering Information

Not all of the speed, package and temperature ranges are available. Please contact your local sales representative or visit [www.cypress.com](http://www.cypress.com) for actual products offered.

| Speed (MHz)         | Ordering Code       | Package Diagram   | Part and Package Type   | Operating Range |            |
|---------------------|---------------------|---|---|-----------------|------------|
| 133                 | CY7C1471V25-133AXC  | 51-85050  | 100-Pin Thin Quad Flat Pack (14 x 20 x 1.4 mm) Pb-Free          | Commercial      |            |
|                     | CY7C1473V25-133AXC  |   |   |                 |            |
|                     | CY7C1471V25-133BZC  | 51-85165  | 165-Ball Fine-Pitch Ball Grid Array (15 x 17 x 1.4 mm)          |                 |            |
|                     | CY7C1473V25-133BZC  |   |   |                 |            |
|                     | CY7C1471V25-133BZXC | 51-85165  | 165-Ball Fine-Pitch Ball Grid Array (15 x 17 x 1.4 mm) Pb-Free  |                 |            |
|                     | CY7C1473V25-133BZXC |   |   |                 |            |
|                     | CY7C1475V25-133BGC  | 51-85167  | 209-Ball Fine-Pitch Ball Grid Array (14 x 22 x 1.76 mm)         |                 |            |
|                     | CY7C1475V25-133BGXC |   | 209-Ball Fine-Pitch Ball Grid Array (14 x 22 x 1.76 mm) Pb-Free |                 |            |
|                     | CY7C1471V25-133AXI  | 51-85050  | 100-Pin Thin Quad Flat Pack (14 x 20 x 1.4 mm) Pb-Free          |                 | Industrial |
|                     | CY7C1473V25-133AXI  |   |   |                 |            |
|                     | CY7C1471V25-133BZI  | 51-85165  | 165-Ball Fine-Pitch Ball Grid Array (15 x 17 x 1.4 mm)          |                 |            |
|                     | CY7C1473V25-133BZI  |   |   |                 |            |
|                     | CY7C1471V25-133BZXI | 51-85165  | 165-Ball Fine-Pitch Ball Grid Array (15 x 17 x 1.4 mm) Pb-Free  |                 |            |
|                     | CY7C1473V25-133BZXI |   |   |                 |            |
| CY7C1475V25-133BGI  | 51-85167            | 209-Ball Fine-Pitch Ball Grid Array (14 x 22 x 1.76 mm)         |   |                 |            |
| CY7C1475V25-133BGXI |                     | 209-Ball Fine-Pitch Ball Grid Array (14 x 22 x 1.76 mm) Pb-Free |   |                 |            |
| 100                 | CY7C1471V25-100AXC  | 51-85050  | 100-Pin Thin Quad Flat Pack (14 x 20 x 1.4 mm) Pb-Free          | Commercial      |            |
|                     | CY7C1473V25-100AXC  |   |   |                 |            |
|                     | CY7C1471V25-100BZC  | 51-85165  | 165-Ball Fine-Pitch Ball Grid Array (15 x 17 x 1.4 mm)          |                 |            |
|                     | CY7C1473V25-100BZC  |   |   |                 |            |
|                     | CY7C1471V25-100BZXC | 51-85165  | 165-Ball Fine-Pitch Ball Grid Array (15 x 17 x 1.4 mm) Pb-Free  |                 |            |
|                     | CY7C1473V25-100BZXC |   |   |                 |            |
|                     | CY7C1475V25-100BGC  | 51-85167  | 209-Ball Fine-Pitch Ball Grid Array (14 x 22 x 1.76 mm)         |                 |            |
|                     | CY7C1475V25-100BGXC |   | 209-Ball Fine-Pitch Ball Grid Array (14 x 22 x 1.76 mm) Pb-Free |                 |            |
|                     | CY7C1471V25-100AXI  | 51-85050  | 100-Pin Thin Quad Flat Pack (14 x 20 x 1.4 mm) Pb-Free          |                 | Industrial |
|                     | CY7C1473V25-100AXI  |   |   |                 |            |
|                     | CY7C1471V25-100BZI  | 51-85165  | 165-Ball Fine-Pitch Ball Grid Array (15 x 17 x 1.4 mm)          |                 |            |
|                     | CY7C1473V25-100BZI  |   |   |                 |            |
|                     | CY7C1471V25-100BZXI | 51-85165  | 165-Ball Fine-Pitch Ball Grid Array (15 x 17 x 1.4 mm) Pb-Free  |                 |            |
|                     | CY7C1473V25-100BZXI |   |   |                 |            |
|                     | CY7C1475V25-100BGI  | 51-85167  | 209-Ball Fine-Pitch Ball Grid Array (14 x 22 x 1.76 mm)         |                 |            |
|                     | CY7C1475V25-100BGXI |   | 209-Ball Fine-Pitch Ball Grid Array (14 x 22 x 1.76 mm) Pb-Free |                 |            |

Package Diagrams

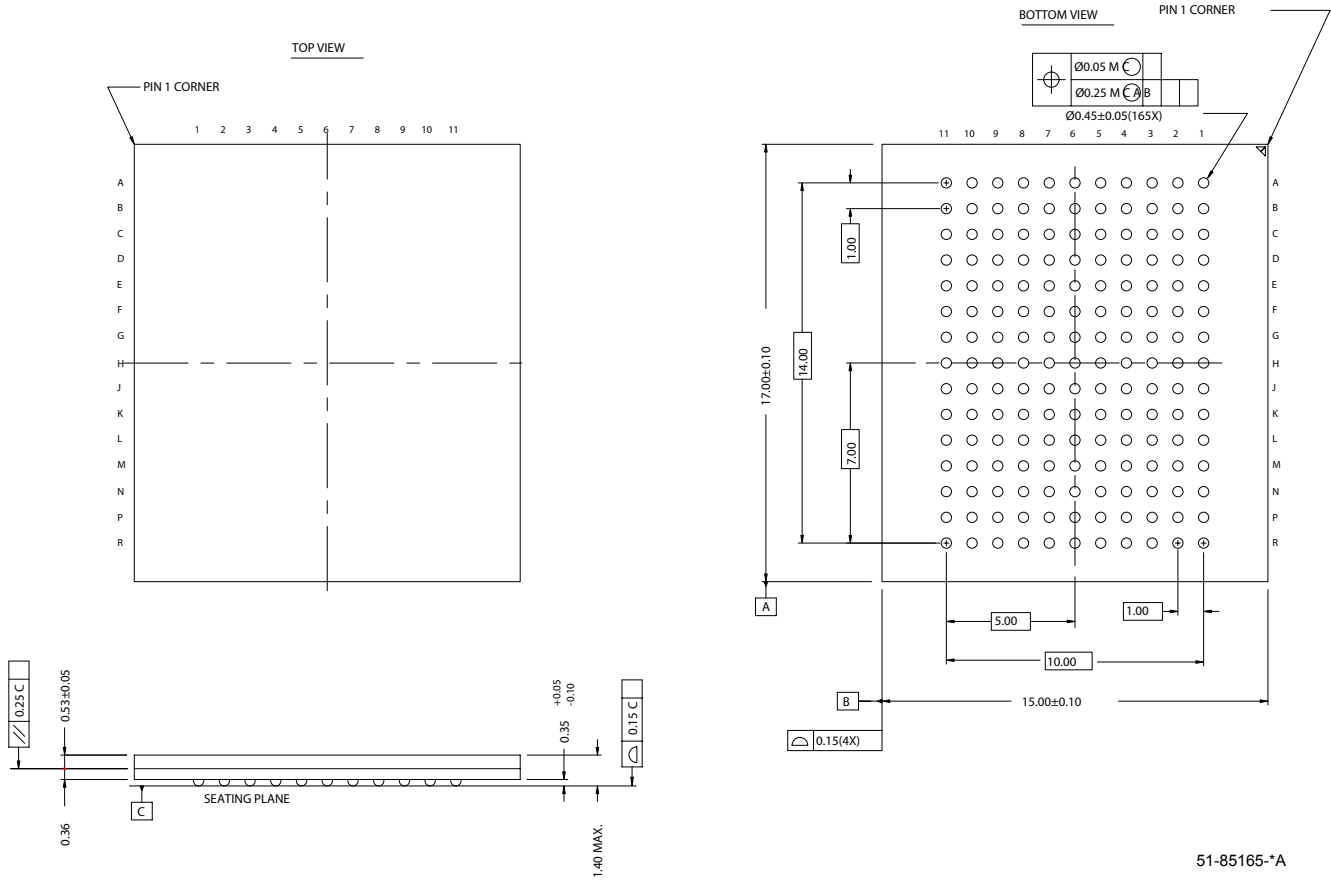
Figure 4. 100-Pin Thin Plastic Quad Flatpack (14 x 20 x 1.4 mm), 51-85050



51-85050-\*B

**Package Diagrams** (continued)

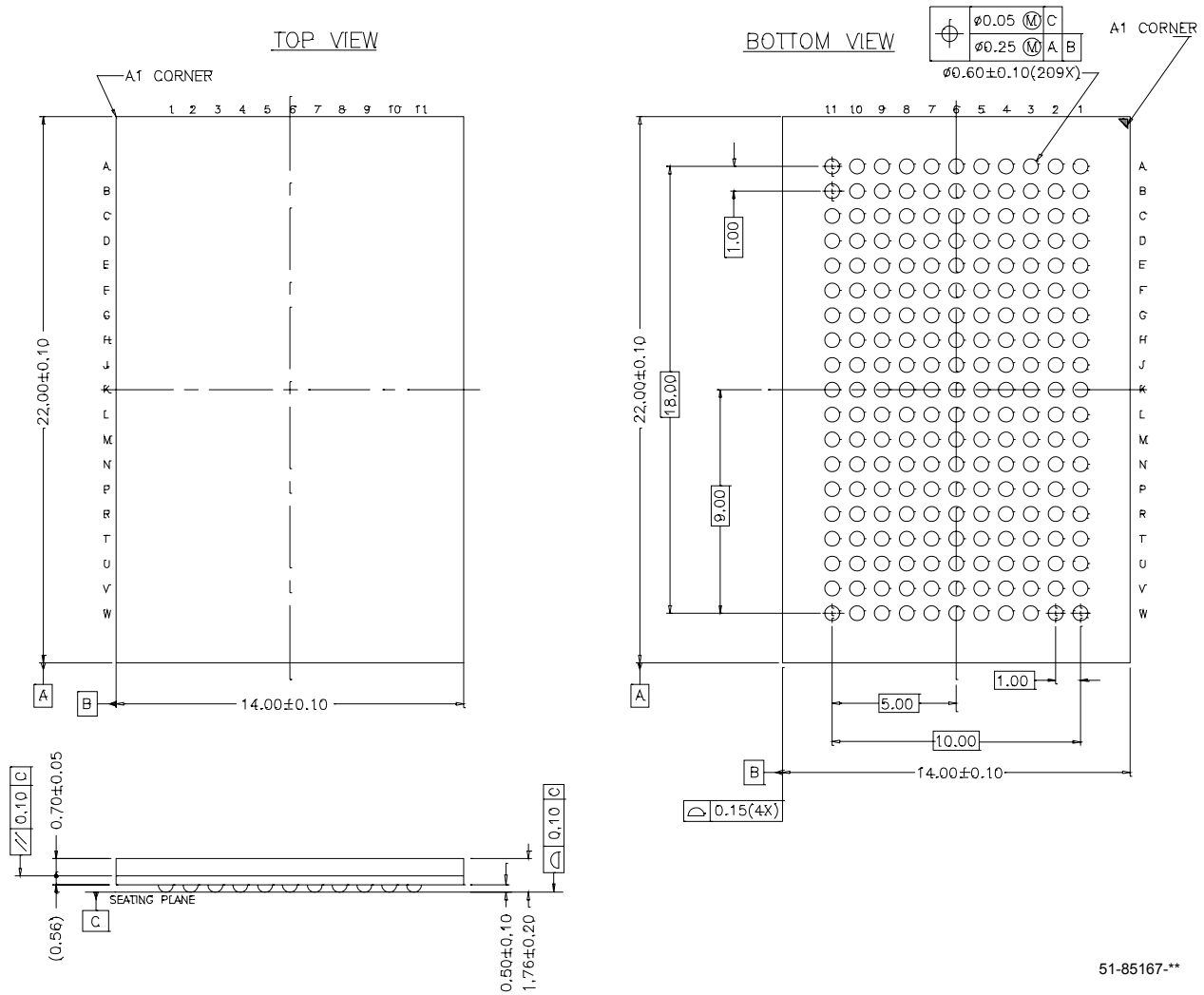
**Figure 5. 165-Ball FBGA (15 x 17 x 1.4 mm), 51-85165**



51-85165-\*A

**Package Diagrams** (continued)

**Figure 6. 209-Ball FBGA (14 x 22 x 1.76 mm), 51-85167**



51-85167-\*\*

NoBL and No Bus Latency are trademarks of Cypress Semiconductor Corporation. ZBT is a trademark of Integrated Device Technology, Inc. All product and company names mentioned in this document are the trademarks of their respective holders.

**Document History Page**

| Document Title: CY7C1471V25/CY7C1473V25/CY7C1475V25, 72-Mbit (2M x 36/4M x 18/1M x 72) Flow-Through SRAM with NoBL™ Architecture<br>Document Number: 38-05287 |         |            |                 |   |
|---|---------|------------|-----------------|---|
| REV.  | ECN NO. | Issue Date | Orig. of Change | Description of Change   |
| **  | 114674  | 08/06/02   | PKS             | New Data Sheet  |
| *A  | 121522  | 01/27/03   | CJM             | Updated features for package offering<br>Updated ordering information<br>Changed Advanced Information to Preliminary  |
| *B  | 223721  | See ECN    | NJY             | Changed timing diagrams<br>Changed logic block diagrams<br>Modified Functional Description<br>Modified "Functional Overview" section<br>Added boundary scan order for all packages<br>Included thermal numbers and capacitance values for all packages<br>Removed 150MHz speed grade offering<br>Included ISB and IDD values<br>Changed package outline for 165FBGA package and 209-Ball BGA package<br>Removed 119-BGA package offering  |
| *C  | 235012  | See ECN    | RYQ             | Minor Change: The data sheets do not match on the spec system and external web  |
| *D  | 243572  | See ECN    | NJY             | Changed ball H2 from V <sub>DD</sub> to NC in the 165-Ball FBGA package in page 6<br>Changed ball R11 in 209-Ball BGA package from DQP <sub>a</sub> to DQP <sub>e</sub> in page 7<br>Modified Capacitance values on page 21   |
| *E  | 299511  | See ECN    | SYT             | Removed 117-MHz Speed Bin<br>Changed $\theta_{JA}$ from 16.8 to 24.63 °C/W and $\theta_{JC}$ from 3.3 to 2.28 °C/W for 100 TQFP Package on Page # 22<br>Added Pb-free information for 100-Pin TQFP, 165 FBGA and 209 BGA Packages<br>Added comment of 'Pb-free BG packages availability' below the Ordering Information   |
| *F  | 323039  | See ECN    | PCI             | Address expansion pins/balls in the pinouts for all packages are modified as per JEDEC standard<br>Added Address Expansion pins in the Pin Definitions Table<br>Modified V <sub>OL</sub> , V <sub>OH</sub> Test Conditions<br>Changed package name from 209-Ball PBGA to 209-Ball FBGA on page# 7<br>Added Industrial temperature range<br>Added Pb-free information in the ordering information table<br>Removed comment of 'Pb-free BG packages availability' below the Ordering Information<br>Updated Ordering Information Table  |
| *G  | 416221  | See ECN    | NXR             | Converted from Preliminary to Final<br>Changed address of Cypress Semiconductor Corporation on Page# 1 from "3901 North First Street" to "198 Champion Court"<br>Changed the description of I <sub>X</sub> from Input Load Current to Input Leakage Current on page# 20<br>Changed the I <sub>X</sub> current values of MODE on page # 20 from -5 μA and 30 μA to -30 μA and 5 μA<br>Changed the I <sub>X</sub> current values of ZZ on page # 20 from -30 μA and 5 μA to -5 μA and 30 μA<br>Changed V <sub>IH</sub> ≤ V <sub>DD</sub> to V <sub>IH</sub> < V <sub>DD</sub> on page # 20<br>Replaced Package Name column with Package Diagram in the Ordering Information table<br>Updated Ordering Information table |

**Document Title: CY7C1471V25/CY7C1473V25/CY7C1475V25, 72-Mbit (2M x 36/4M x 18/1M x 72) Flow-Through SRAM with NoBL™ Architecture**  
**Document Number: 38-05287**

| REV. | ECN NO. | Issue Date | Orig. of Change | Description of Change  |
|------|---------|------------|-----------------|--|
| *H   | 472335  | See ECN    | VKN             | Corrected the typo in the pin configuration for 209-Ball FBGA pinout (Corrected the ball name for H9 to V <sub>SS</sub> from V <sub>SSQ</sub> ).<br>Added the Maximum Rating for Supply Voltage on V <sub>DDQ</sub> Relative to GND.<br>Changed t <sub>TH</sub> , t <sub>TL</sub> from 25 ns to 20 ns and t <sub>TDOV</sub> from 5 ns to 10 ns in TAP AC Switching Characteristics table.<br>Updated the Ordering Information table. |
| *I   | 1274732 | See ECN    | VKN/AESA        | Corrected typo in the "NOP, STALL and DESELECT Cycles" waveform  |





Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.